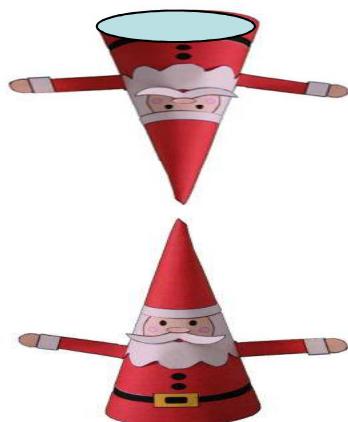


Handedness resolved magneto-infrared spectroscopy of 2D and 3D Dirac materials



Alexey B. Kuzmenko
University of Geneva

20.01.17

Winter School
New Frontiers in 2D materials:
Approaches & Applications



UNIVERSITÉ
DE GENÈVE

FNSNF

FONDS NATIONAL SUISSE
DE LA RECHERCHE SCIENTIFIQUE

Acknowledgments

University of Geneva

Iris Crassee

Julien Levallois

Jean-Marie Poumirol

Pieter de Visser

Ievgeniia Nedoliuk

Michael Tran

Dirk van der Marel

Jérémie Teyssier

University of Zaragoza

Tetiana Slipchenko

Luis Martin-Moreno

University of Michigan

Ctirad Uher

LCNMI, Grenoble

Milan Orlita

ETHZ (Zurich)

Peter Q. Liu

Jérôme Faist

EPFL (Lausanne)

Michele Tamagnone

Clara Moldovan

Julien Perruseau-Carrier

Juan Mosig

nanoGUNE (San-Sebastian)

Alexey Nikitin



UNIVERSITÉ
DE GENÈVE

FNSNF

FONDS NATIONAL SUISSE
DE LA RECHERCHE SCIENTIFIQUE

Outline

- + Handedness resolved magneto-infrared spectroscopy
- + Anomalous magnetic circular dichroism (MCD) and valley-polarized magneto-absorption in **bismuth**
- + Electrically controlled terahertz MCD and Faraday rotation in **graphene**

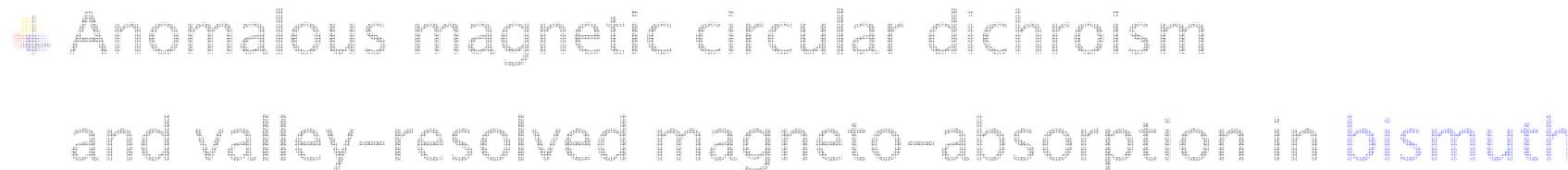


UNIVERSITÉ
DE GENÈVE

FNSNF
FONDS NATIONAL SUISSE
DE LA RECHERCHE SCIENTIFIQUE

Outline

⊕ Handedness resolved magneto-infrared spectroscopy



⊕ Electrically controlled terahertz magneto-optics



UNIVERSITÉ
DE GENÈVE

FNSNF
FONDS NATIONAL SUISSE
DE LA RECHERCHE SCIENTIFIQUE

Why handedness resolved IR/THz spectroscopy?

- Magnetic-circular dichroism (MCD) is a very important parameter to identify magneto-optical transitions
- Measuring MCD in the far-infrared/THz directly is very challenging (no broadband waveplates, or photoelastic modulators)

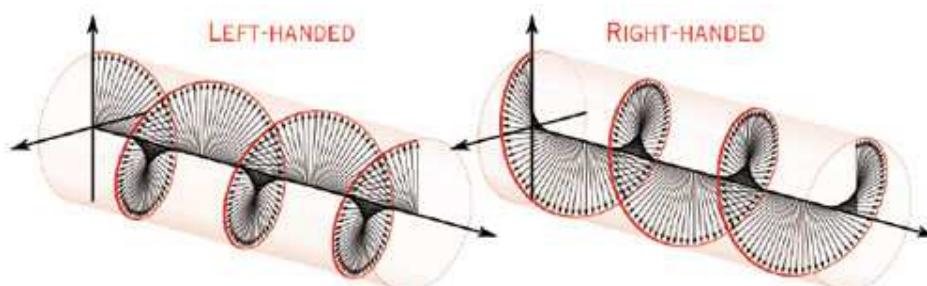
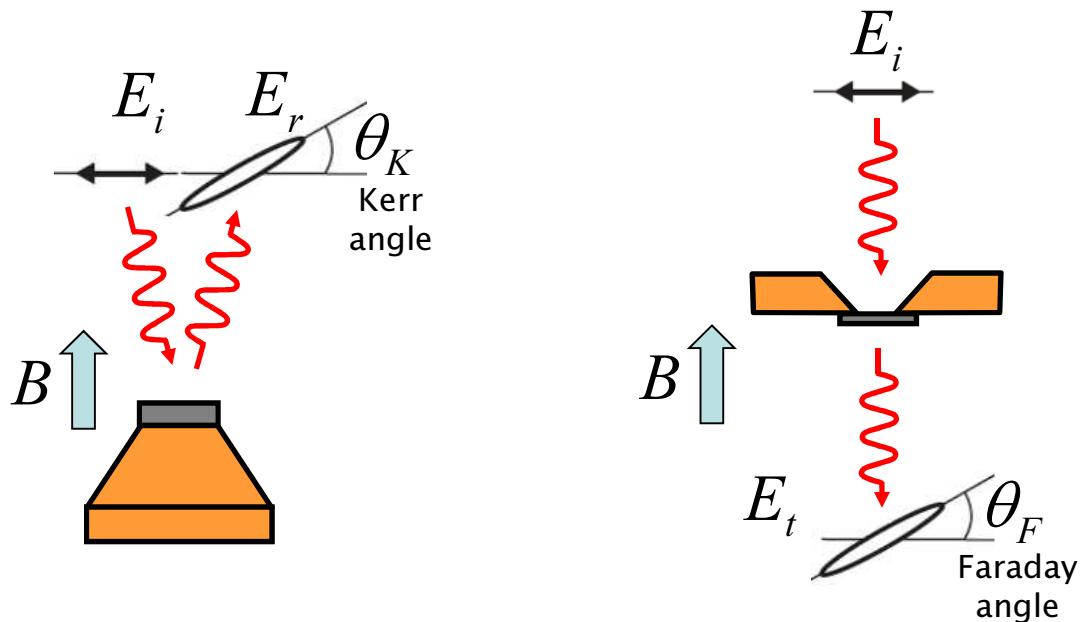


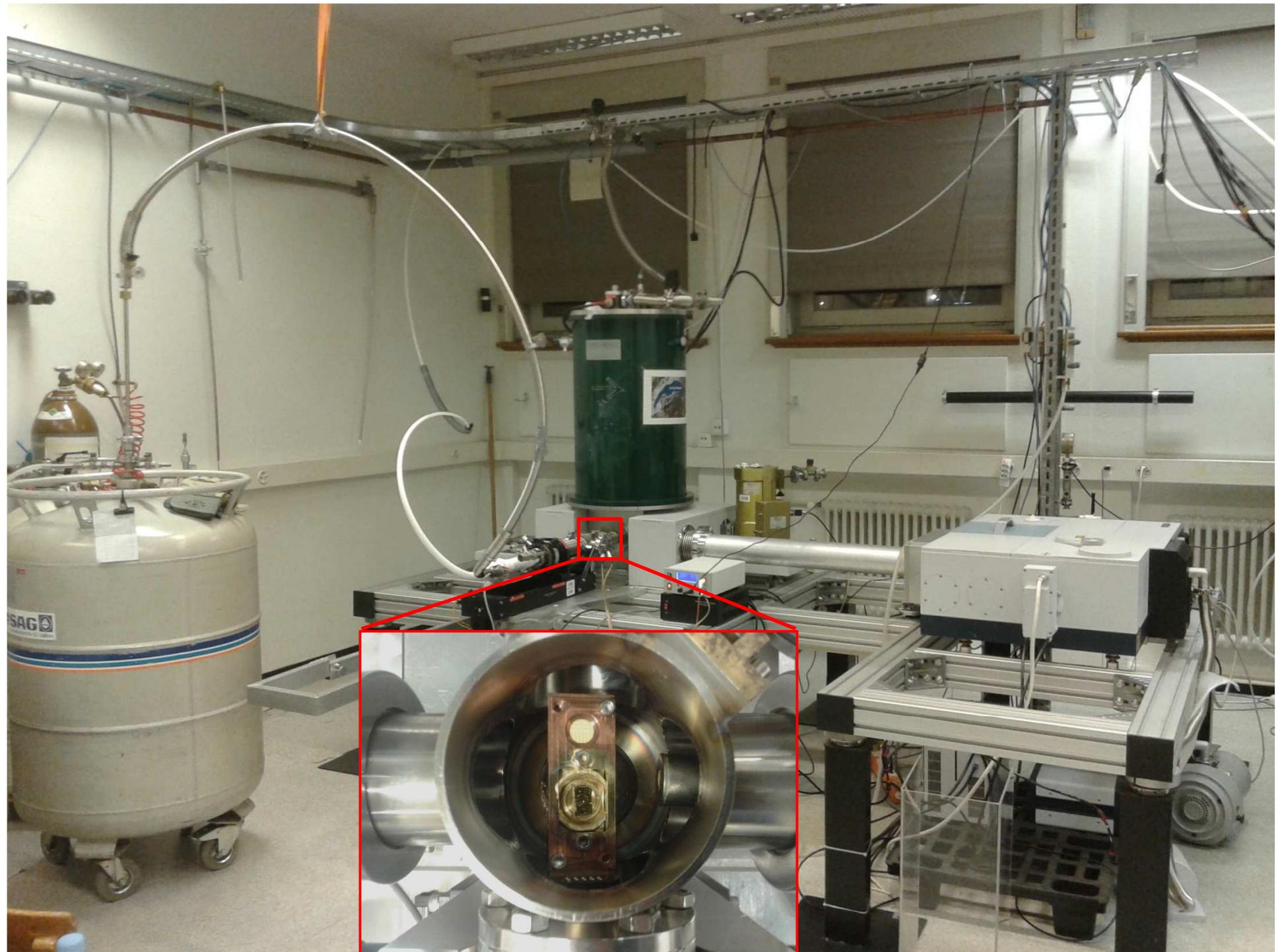
Image from: <http://blog.atlasrfidstore.com/choose-right-rfid-antenna>

Magneto-optical THz experiment in Geneva



- FTIR or time-domain THz spectroscopy
- Magnetic field up to 7 T (superconducting coil)
- Transmission/reflection
- Faraday rotation / Kerr rotation





Magneto-optical Kramers–Kronig analysis (MOKKA)

Linear magneto-optical response

is determined by the transmission tensor:

or equivalently (in the circular basis): $t_{\pm} = t_{xx} \pm it_{xy}$

$$\hat{t}(\omega, B) = \begin{pmatrix} t_{xx} & t_{xy} \\ -t_{xy} & t_{xx} \end{pmatrix}$$

L. Onsager, Phys. Rev. 37, 405 (1931)

We can directly measure:

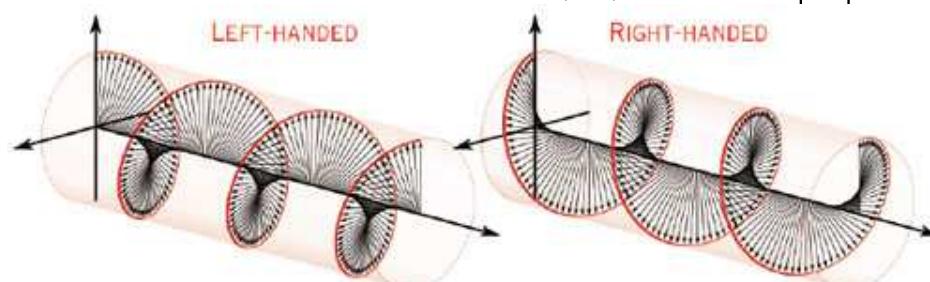
Transmission (for linear polarized light) $T = \frac{|t_+|^2 + |t_-|^2}{2}$

Faraday rotation: $\theta_F = \frac{1}{2} \operatorname{Arg}\left(\frac{t_-}{t_+}\right)$

Using a magneto-optical Kramers–Kronig analysis (MOKKA), we obtain:

Transmission (for circular polarized light): $T_+ = |t_+|^2 \quad T_- = |t_-|^2$

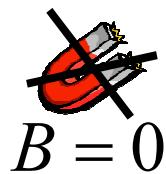
Ellipticity/MCD



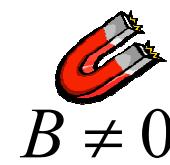
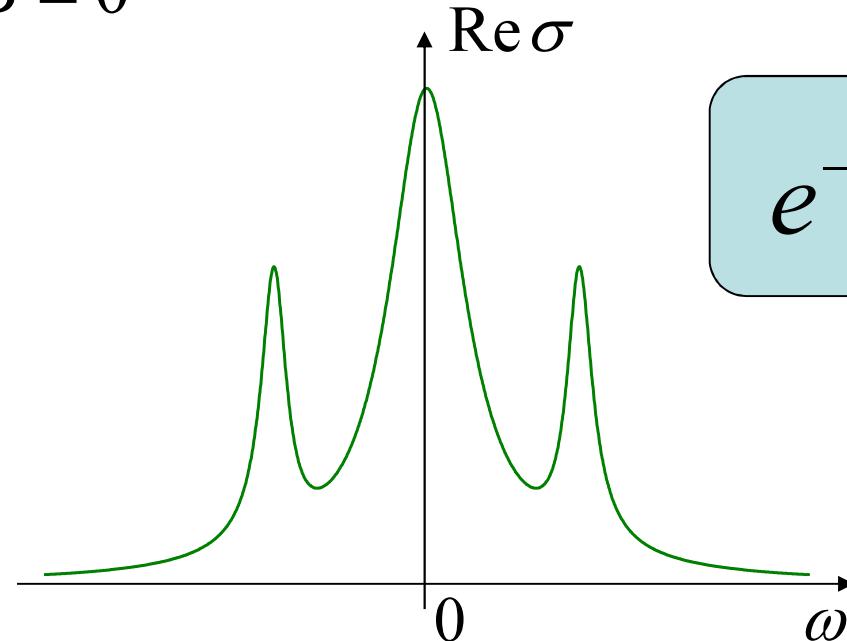
Basic assumptions for MOKKA

1. Magneto-optical dielectric function $\epsilon(\omega, B)$ is:
 - ✚ local (q -independent)
 - ✚ isotropic in the plane $\perp B$ -field
2. Magnetic permeability $\mu(\omega, B)$ is negligible
3. Magnetoelectric (multiferroic, axionic etc.) terms are negligible
4. B -field and light-propagation are both normal to the sample surface

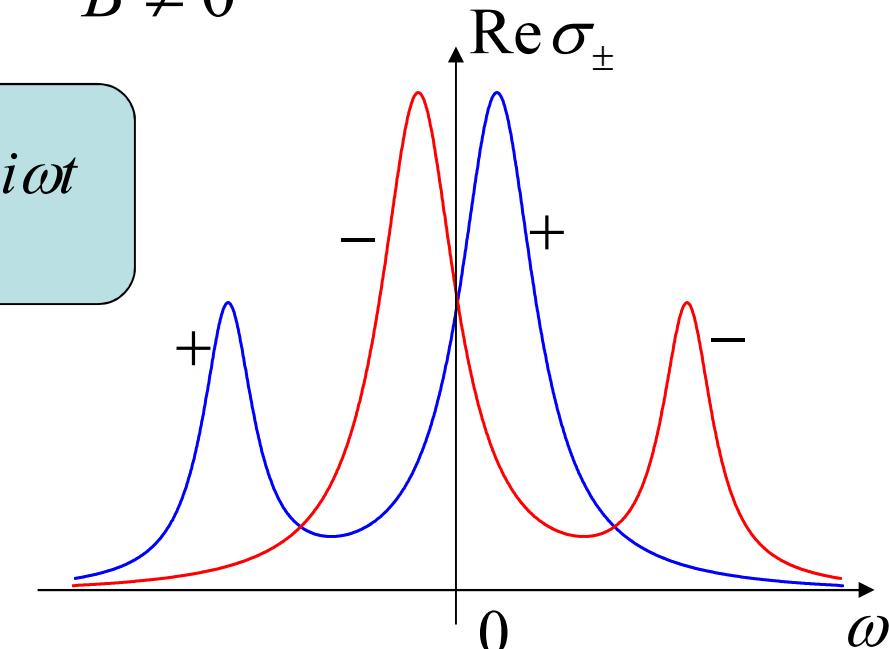
Parity relations for MO conductivity



Time-reversal symmetry
is preserved:

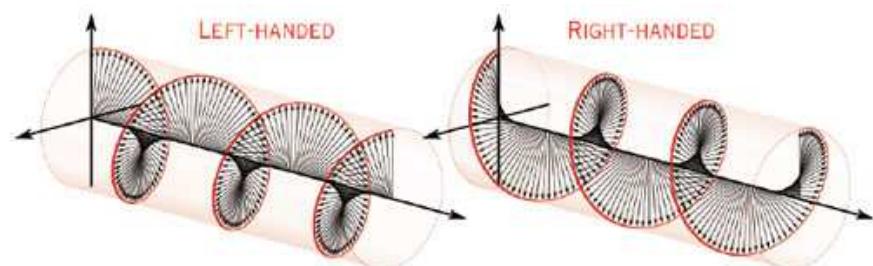


Time-reversal symmetry
is broken:



$$\sigma(-\omega) = \sigma^*(\omega)$$

$$\sigma_{\pm}(-\omega) = \sigma_{\mp}^*(\omega)$$



Standard KK analysis of reflectivity



complex reflectivity (unknown)

$$r(\omega) = \sqrt{R(\omega)} e^{i\theta(\omega)}$$

real reflectivity (known)

$$R(\omega)$$

Consider the function:



$$f(\omega) = \ln r(\omega) = \ln \sqrt{R(\omega)} + i\theta(\omega)$$

If f is analytic (meromorphic (e.g. for normal reflectivity from a bulk sample)) then the KK relation applies:

**Does not apply
to magneto-optics !**

$$\theta(\omega) = -\frac{1}{\pi} \varphi \int_{-\infty}^{\infty} \frac{\ln \sqrt{R(x)}}{x - \omega} dx + \pi$$

This proves
the theorem:

$R(\omega)$ in $(0, +\infty)$ determines uniquely $r(\omega)$

For a reliable KK analysis one has to measure in a broad range
and/or use additional measurements, such as ellipsometry

MOKKA (direct integration)



complex reflectivity (unknown)

$$r_{\pm}(\omega) = \sqrt{R_{\pm}(\omega)} e^{i\theta_{\pm}(\omega)}$$

real reflectivity (known)

$$R(\omega) = \frac{R_+(\omega) + R_-(\omega)}{2}$$

Kerr angle (known)

$$\theta_K(\omega) = \frac{\theta_-(\omega) - \theta_+(\omega)}{2}$$

Consider the function:

$$f(\omega) = \ln \left(\frac{r_-(\omega)}{r_+(\omega)} \right) = \frac{1}{2} \ln c(\omega) + 2i\theta_K(\omega)$$

↑ unknown ↓ known

where $c(\omega) = \frac{R_-(\omega)}{R_+(\omega)}$
is circular-dichroism ratio

1st KK relation:

$$c(\omega) = \exp \left\{ \frac{8\omega}{\pi} \wp \int_0^\infty \frac{\theta_K(x)}{x^2 - \omega^2} dx \right\} \Rightarrow R_+(\omega) = \frac{2R(\omega)}{1 + c(\omega)} \Rightarrow R_-(\omega) = \frac{2c(\omega)R(\omega)}{1 + c(\omega)}$$

2nd KK relation: $\theta_{\pm}(\omega) = -\frac{1}{\pi} \wp \int_{-\infty}^\infty \frac{\ln \sqrt{R_{\pm}(x)}}{x - \omega} dx + \pi$

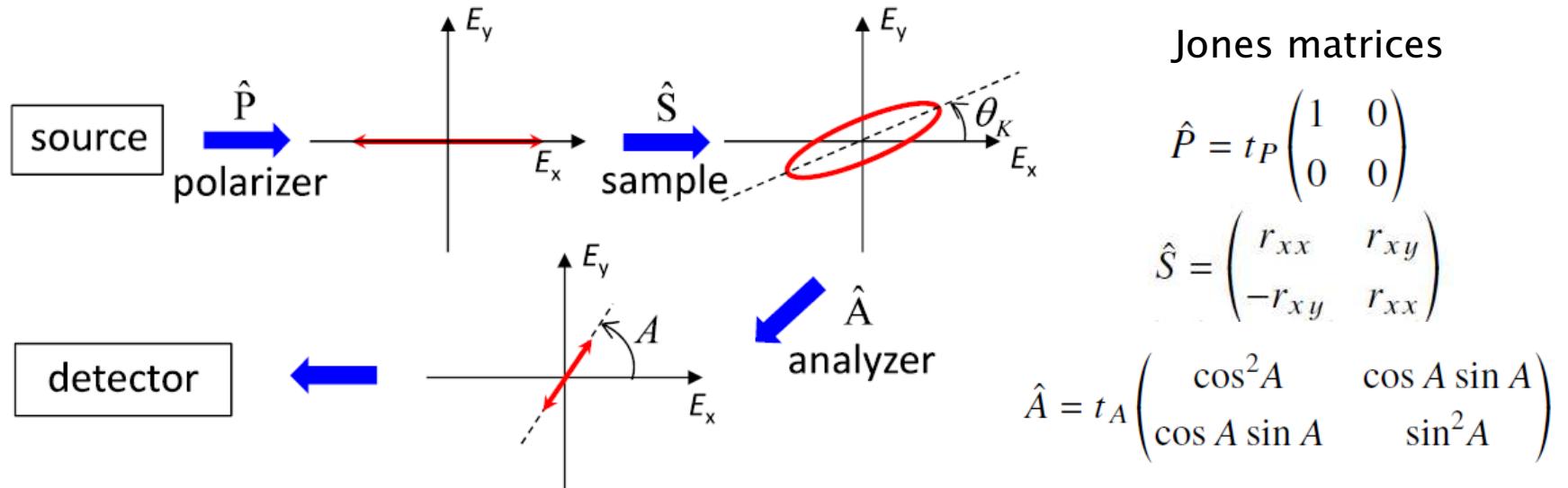
Since

$$R_{\pm}(-\omega) = R_{\mp}(\omega) \Rightarrow \theta_{\pm}(\omega) = -\frac{\omega}{\pi} \wp \int_0^\infty \frac{\ln \sqrt{R_+(x)R_-(x)}}{x^2 - \omega^2} dx + \pi \mp \theta_K(\omega)$$

This proves
the theorem:

R(ω) and $\theta_K(\omega)$ in $(0, +\infty)$ determine uniquely $r_{\pm}(\omega)$

Polarimetric experiment “fixed polarizer, rotating analyser” *



$$I_A = C_A \frac{R + \tilde{R} \cos(2A - 2\theta_K)}{2}$$

$$\text{where } R(\omega) = \frac{R_+(\omega) + R_-(\omega)}{2}$$

$$\tilde{R}(\omega) = \sqrt{R_+(\omega)R_-(\omega)}$$

Ellipsometry at normal incidence !

* The same applies to the case «rotating polarizer, fixed analyzer»

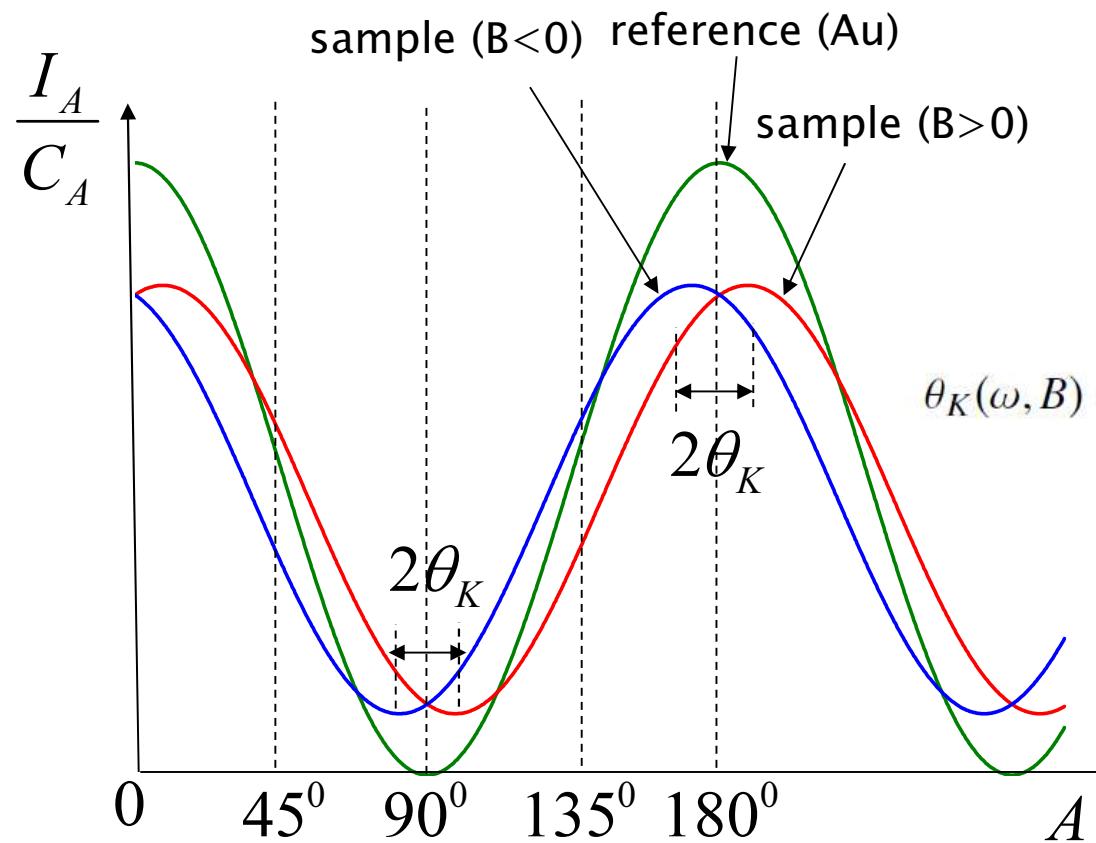
Extracting reflectivity and Kerr angle*

$$I_A = C_A \frac{R + \tilde{R} \cos(2A - 2\theta_K)}{2}$$

where

$$R(\omega) = \frac{R_+(\omega) + R_-(\omega)}{2}$$

$$\tilde{R}(\omega) = \sqrt{R_+(\omega)R_-(\omega)}$$



Fast protocol
(accurate if $\theta_K < 0.2$ rad)

$$R(\omega, B) \approx \frac{I_0(\omega, B)}{I_{0,ref}(\omega, B)}$$

$$\theta_K(\omega, B) \approx \frac{1}{8} \left[\frac{\rho_{+45}(\omega, B)}{\rho_{+45,ref}(\omega, B)} - \frac{\rho_{-45}(\omega, B)}{\rho_{-45,ref}(\omega, B)} \right]$$

$$\text{where } \rho_{\pm 45}(\omega, B) = \frac{I_{\pm 45}(\omega, +B)}{I_{\pm 45}(\omega, -B)}$$

only measurements
at $A=0, 45$ and -45
needed !

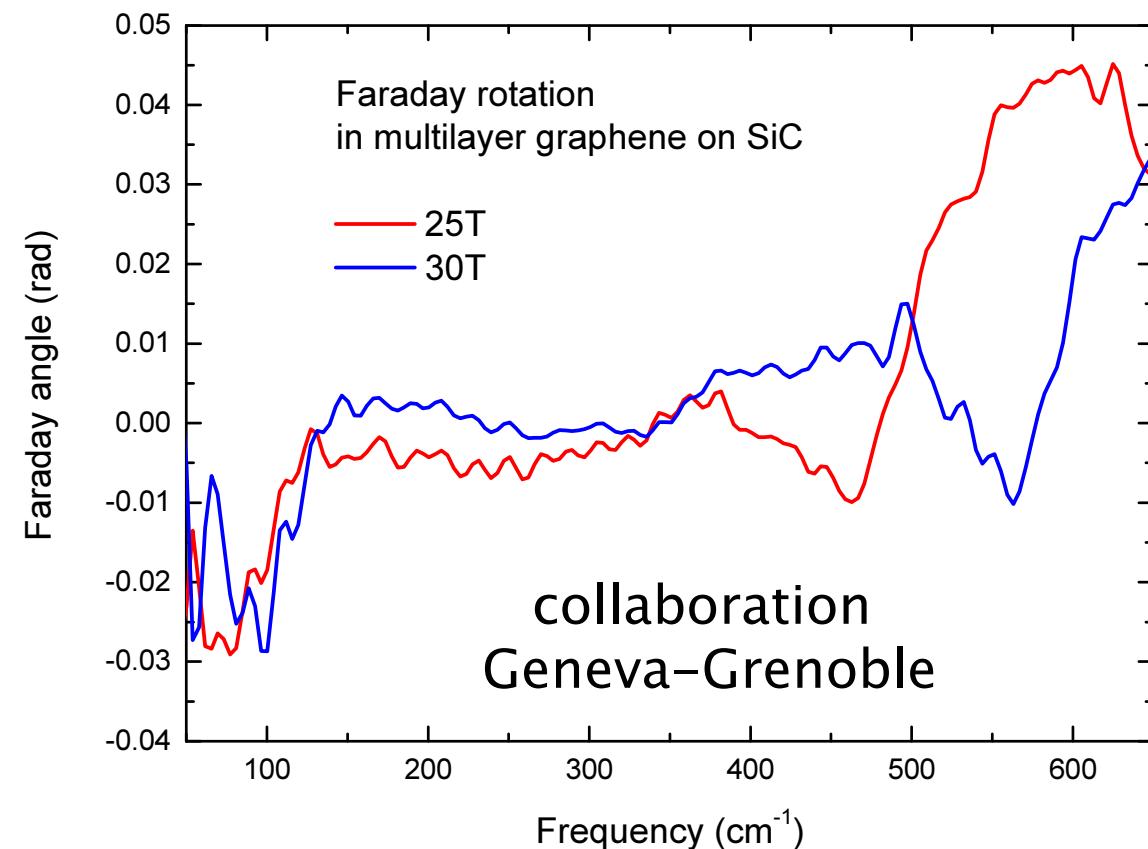
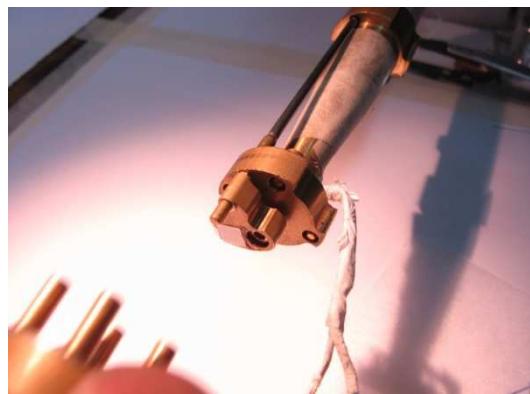
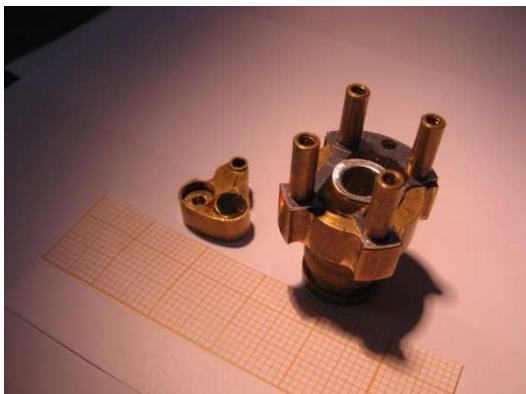
* The same applies to the case of transmission and Faraday angle

J. Levallois et al., Rev. Sci. Instrum. 86, 033906 (2015)

Advantages of MOKKA

- ✚ broadband (based on polarizers only)
- ✚ can be applied at high magnetic fields (polarizers are fixed)

The first Faraday rotation
spectroscopic measurement at **30 T**



Advantages of MOKKA



Outline

- Handedness resolved magneto-infrared spectroscopy
- Anomalous magnetic circular dichroism
and valley-resolved magneto-absorption in **bismuth**
- Electrically controlled terahertz magneto-optical
phenomena in graphene



UNIVERSITÉ
DE GENÈVE

FNSNF
FONDS NATIONAL SUISSE
DE LA RECHERCHE SCIENTIFIQUE

In the beginning was the Bismuth...

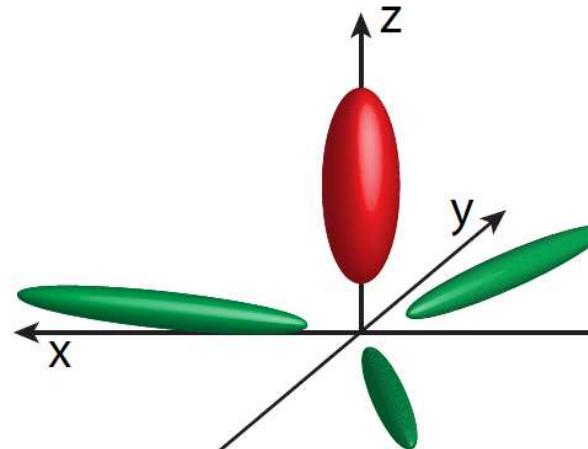
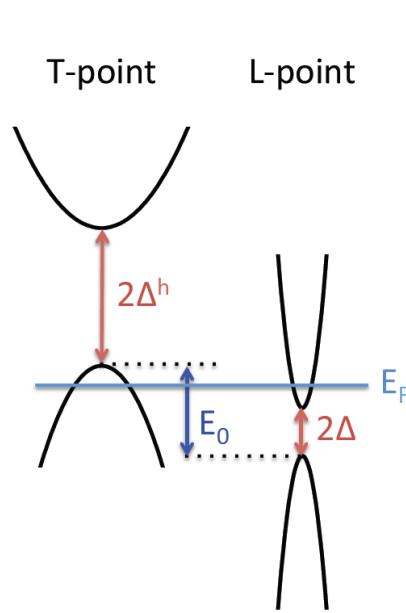


Image from: Z. Zhu et al. PRB 84, 115137 (2011).

- Ultralow-density 3D-Dirac semimetal
- Strong spin-orbit coupling
- Huge band-mass anisotropy (> 200)
- Topological insulator when alloyed with Sb
- ...

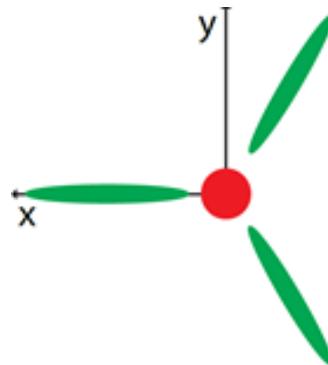
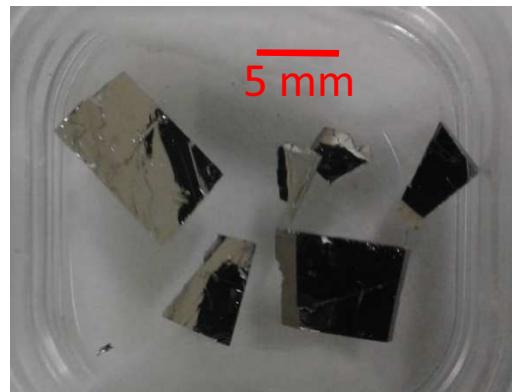
Table I. Chronological table of phenomena discovered first in bismuth.

Year	Discovery
1778	Diamagnetism (Brugmans; named by Faraday in 1845)
1821	Seebeck effect
1886	Nernst effect (Ettingshausen and Nernst)
1928	Kapitza's law of magnetoresistance
1930	Shubnikov-de Haas effect
1930	de Haas-van Alphen effect
1955	Cyclotron resonance in metals (Galt)
1963	Oscillatory magnetostriction (Green and Chandrasekhar)

Table from: Fuseya et al. JPSJ 84, 012001 (2015)

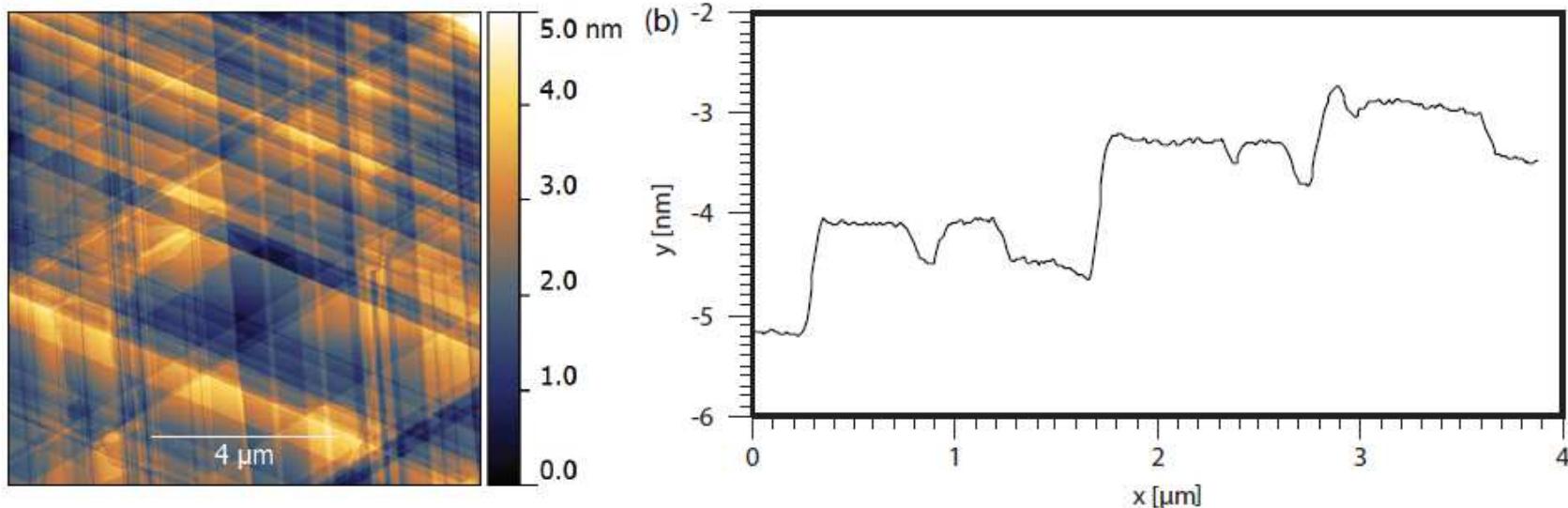
Bismuth crystals

Very soft material, cleaved in liquid nitrogen, always on the trigonal plane



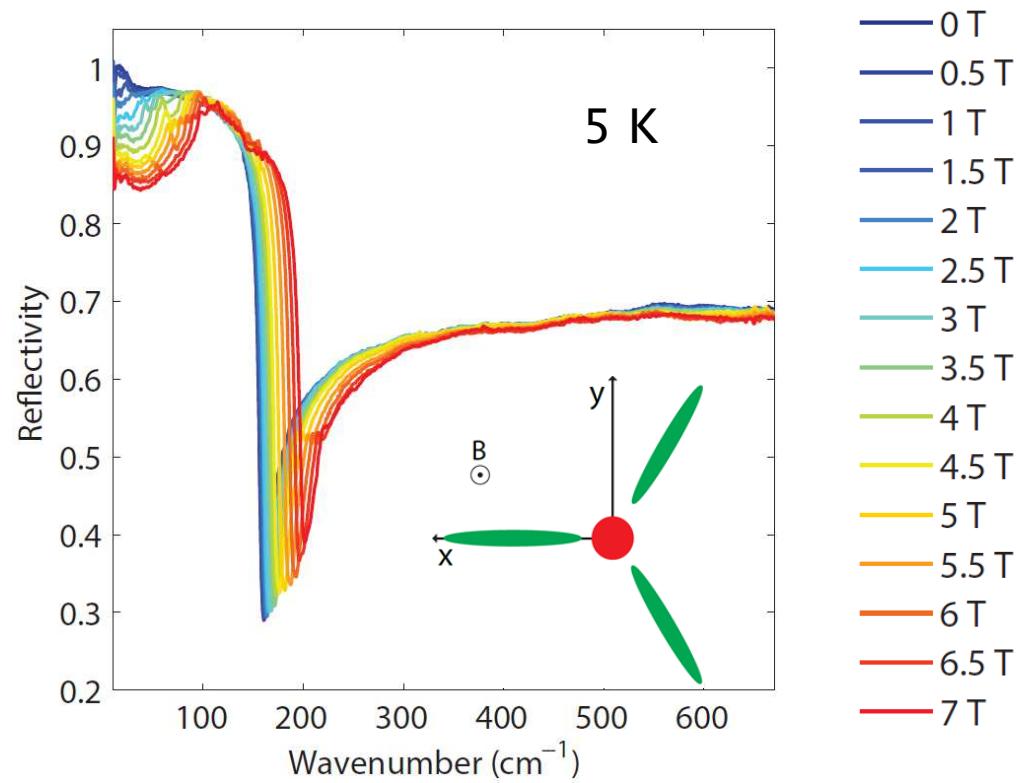
- Atomically flat surface
- Steps 0.4, 0.8 and 1.2 nm
(1/3, 2/3 and 1 unit-cell)

AFM topography

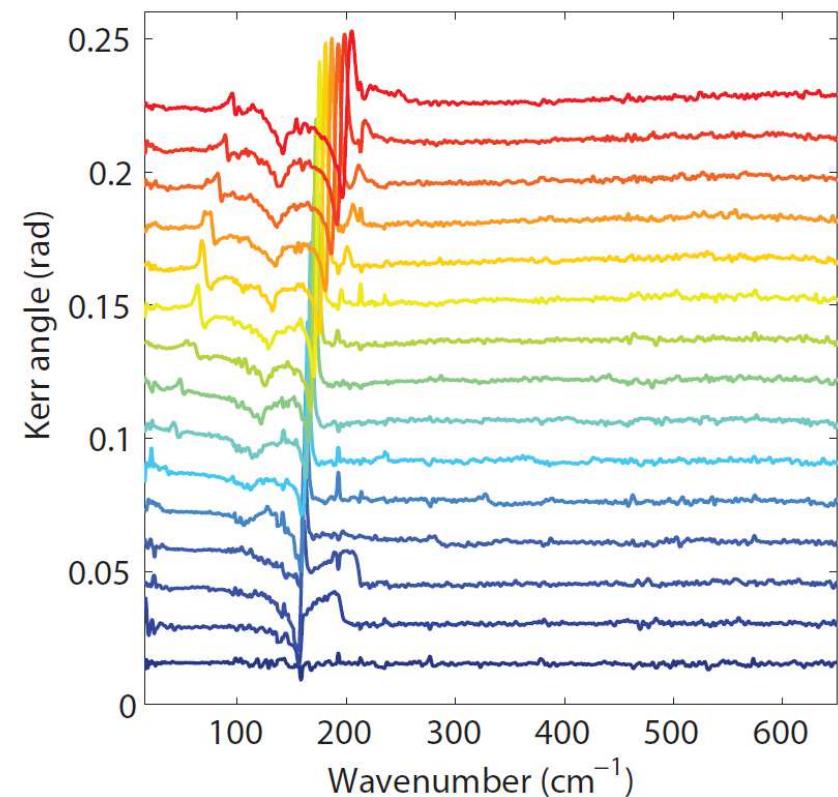


Far-IR reflectivity + Kerr rotation on bismuth

Magneto-reflectivity



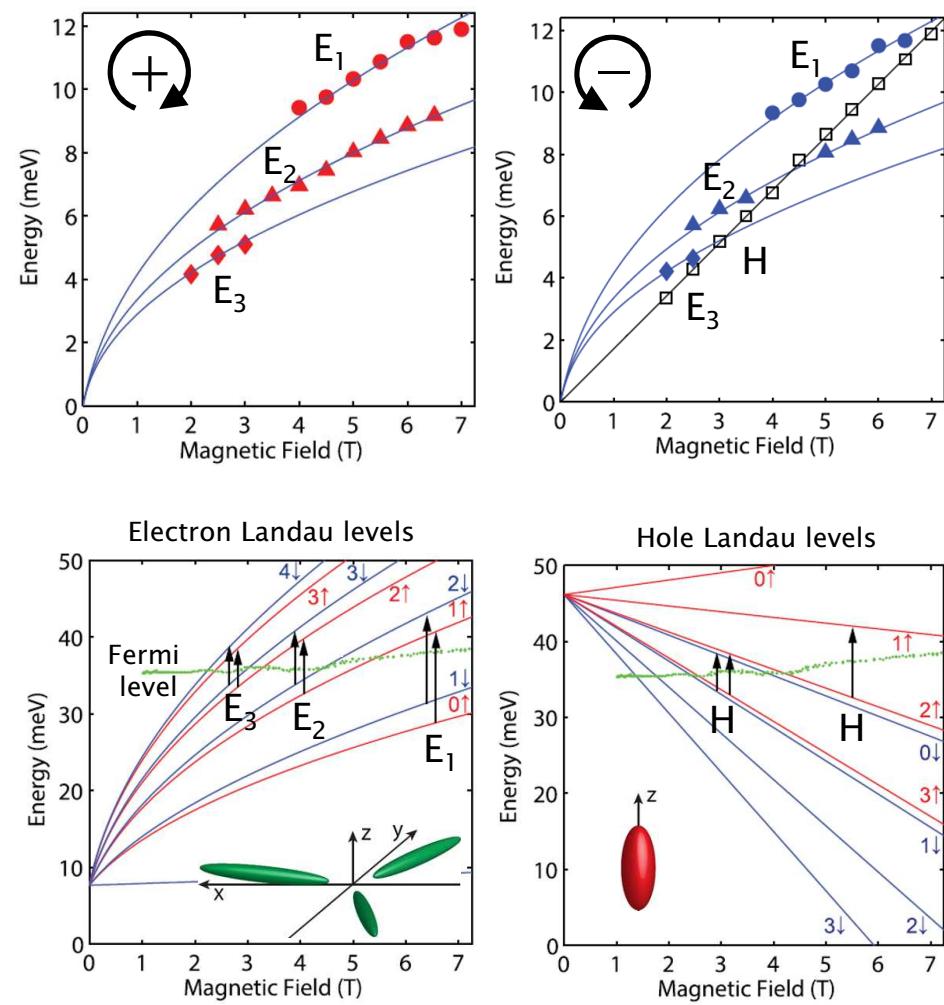
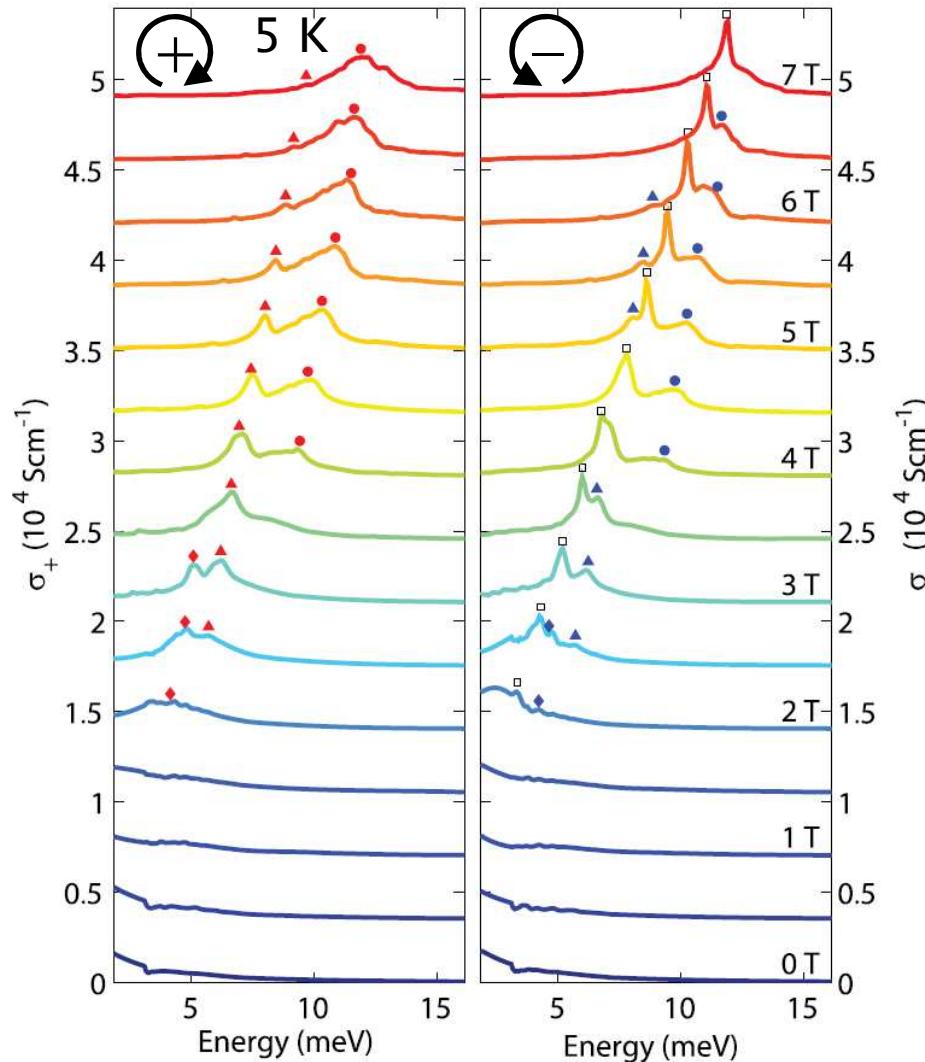
Kerr rotation



Why not done before ?

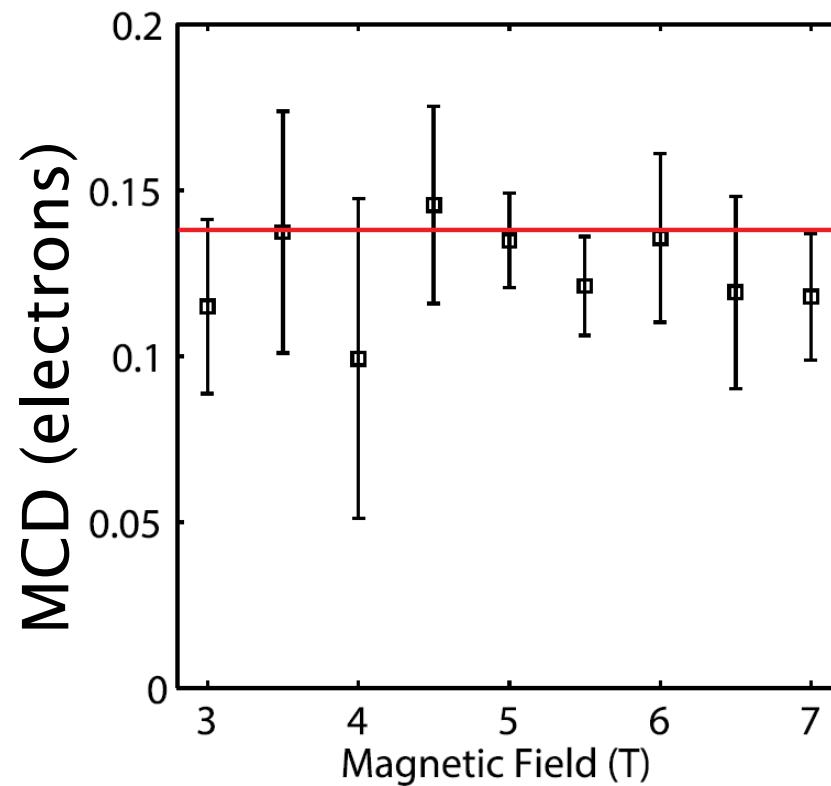
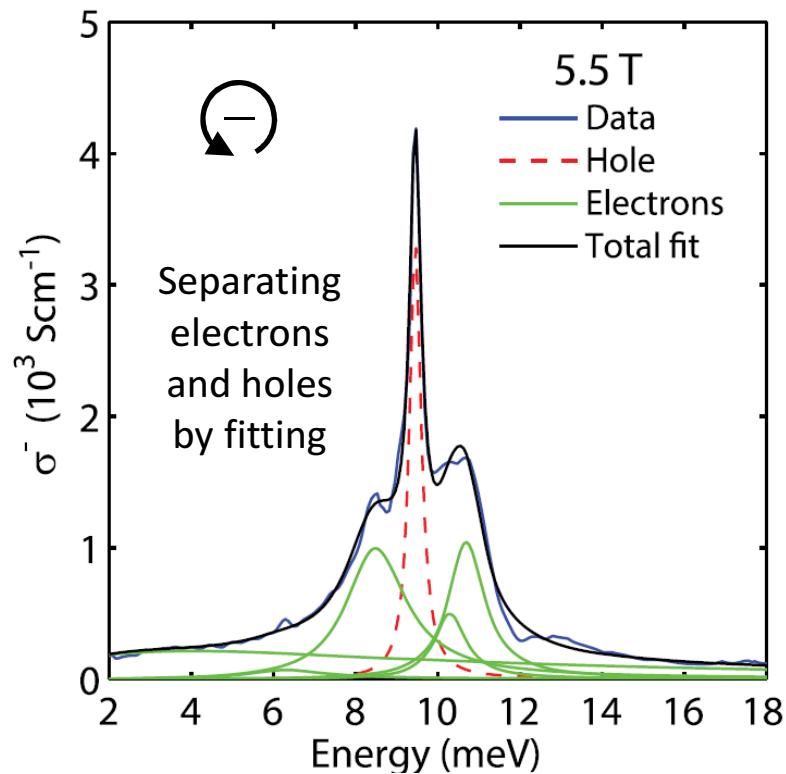
- Spectroscopic (FTIR) experiments never combined with Kerr rotation
- Handedness-resolved experiments only at fixed (laser) wavelengths

Handedness-resolved magneto-optical conductivity of bismuth (from MOKKA)



Why electron LLs in both polarizations ???

Magnetic circular dichroism (MCD) in bismuth



$$\text{MCD} = \frac{\sigma_+ - \sigma_-}{\sigma_+ + \sigma_-} = \begin{cases} 100\% & \text{(holes)} \\ 13 \pm 1\% & \text{(electrons)} \end{cases}$$

Hugely suppressed for electrons !

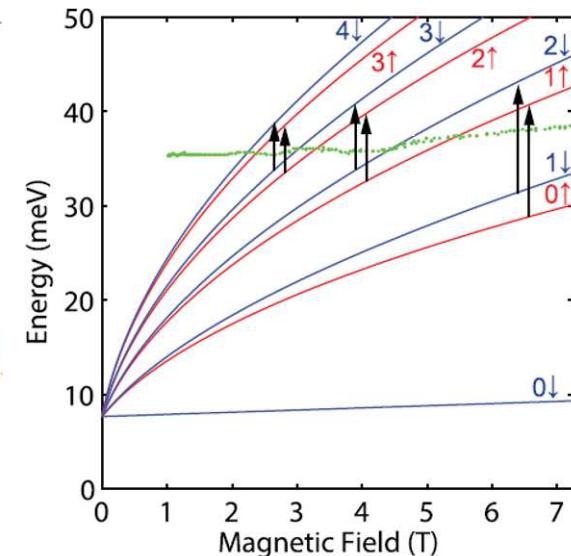
3D Dirac gapped Hamiltonian and LLs in Bi

$$H_e(B) = \begin{bmatrix} \Delta & 0 & i\hbar v_z k_z & i\frac{\sqrt{2}}{l_B}\hbar v a^- \\ 0 & \Delta & i\frac{\sqrt{2}}{l_B}\hbar v a^+ & -i\hbar v_z k_z \\ -i\hbar v_z k_z & -i\frac{\sqrt{2}}{l_B}\hbar v a^- & -\Delta & 0 \\ -i\frac{\sqrt{2}}{l_B}\hbar v a^+ & i\hbar v_z k_z & 0 & -\Delta \end{bmatrix} \quad \begin{aligned} v &= (\Delta/m_c)^{1/2} \\ v_z &= (\Delta/m_z)^{1/2} \\ l_B &= (\hbar/eB)^{1/2} \\ &\text{- magnetic length} \end{aligned}$$

Ladder operators: $k_x + ik_y \rightarrow \frac{l_B}{\sqrt{2}}a^+$, $k_x - ik_y \rightarrow \frac{l_B}{\sqrt{2}}a^-$

Landau levels:

$$E_e(n, s, B) = \sqrt{\Delta^2 + 2\Delta\left(n + \frac{1}{2} + s\right)\frac{\hbar e B}{m_c} + sg\mu_B B}$$



Model agrees perfectly with Nernst, dHvA, SdH... effects
Therefore LLs, $E_F(B)$, DoS(B) are for sure correct

3D Dirac gapped Hamiltonian and LLs in Bi

Landau levels:

$$E_e(n, s, B) = \sqrt{\Delta^2 + 2\Delta\left(n + \frac{1}{2} + s\right)\frac{\hbar eB}{m_c}} + sg\mu_B B$$

Theory:

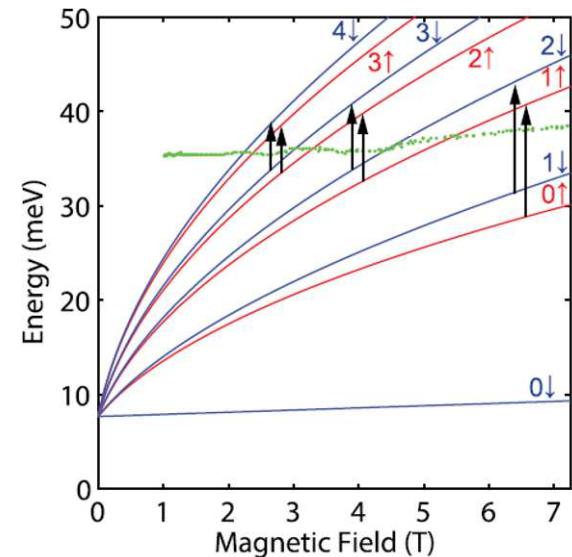
Selection rules for LL transitions::

$$\Delta s = 0$$

RH circular: $\Delta n = +1$
LH circular: $\Delta n = -1$

$$\begin{aligned}\sigma_+ &\neq 0 \\ \sigma_- &= 0\end{aligned}$$

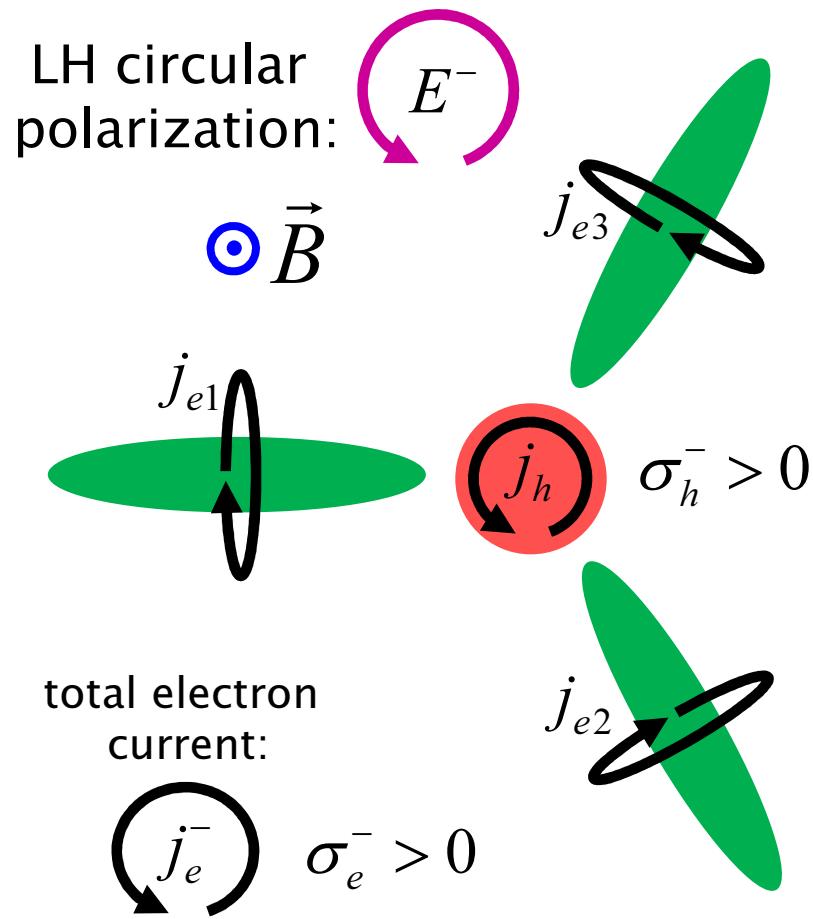
$$\text{MCD} = 100\%$$



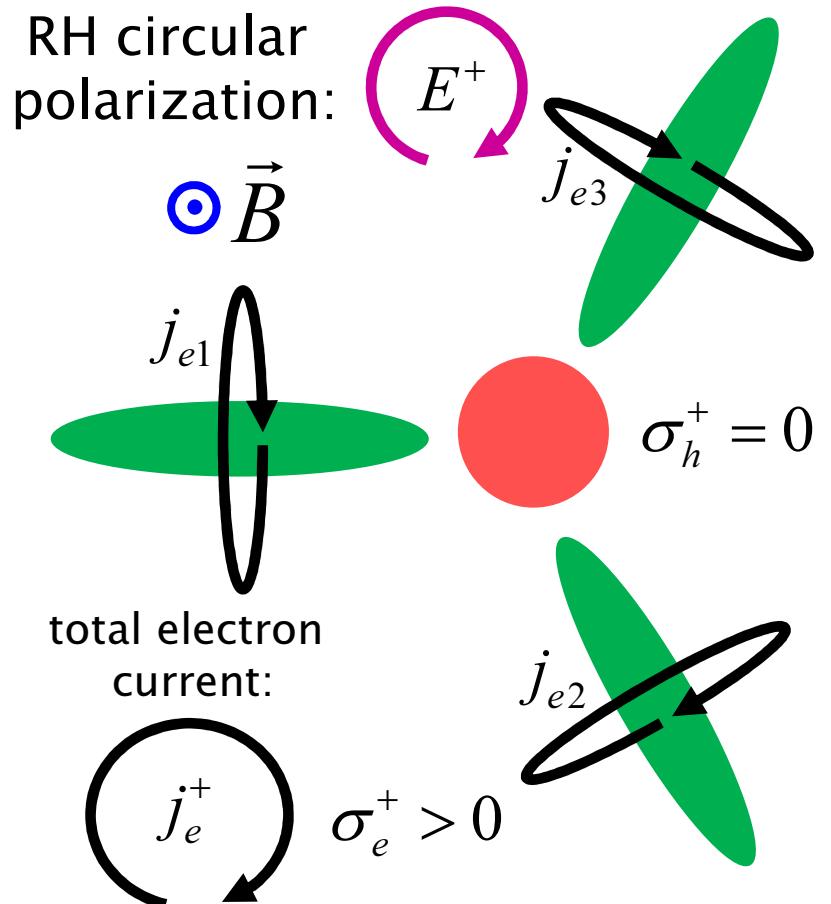
Experiment: MCD = 13%

Does not explain the suppression of MCD !!!

Mechanism of electron–MCD reduction in Bi



$$MCD(\text{holes}) = \frac{\sigma_h^+ - \sigma_h^-}{\sigma_h^+ + \sigma_h^-} = 100\%$$



$$MCD(\text{electr.}) = \frac{\sigma_e^+ - \sigma_e^-}{\sigma_e^+ + \sigma_e^-} \ll 100\%$$

Anisotropic mass as anisotropic metric

$\alpha = (m_x/m_y)^{1/2}$ - anisotropy parameter (≈ 15 in Bi)

Mass anisotropy is equivalent to anisotropic spatial metric

$$\begin{aligned}\tilde{x} &= \alpha^{-1/2}x, \quad \tilde{y} = \alpha^{1/2}y \\ \tilde{k}_x &= \alpha^{1/2}k_x, \quad \tilde{k}_y = \alpha^{-1/2}k_y\end{aligned}$$

Anisotropic problem can be mapped isotropic problem:

$$\tilde{k}_x + i\tilde{k}_y \rightarrow \frac{l_B}{\sqrt{2}}\tilde{a}^+, \quad \tilde{k}_x - i\tilde{k}_y \rightarrow \frac{l_B}{\sqrt{2}}\tilde{a}^-$$

LL energies thus remain the same: $\tilde{E}_n(B, k_z) = E_n(B, k_z)$

But LL wavefunctions are scaled :

$$\tilde{\Psi}_n(B, x, y, k_z) = \Psi_n\left(B, \alpha^{-1/2}x, \alpha^{1/2}y, k_z\right)$$

Magneto-optical conductivity (in one valley):

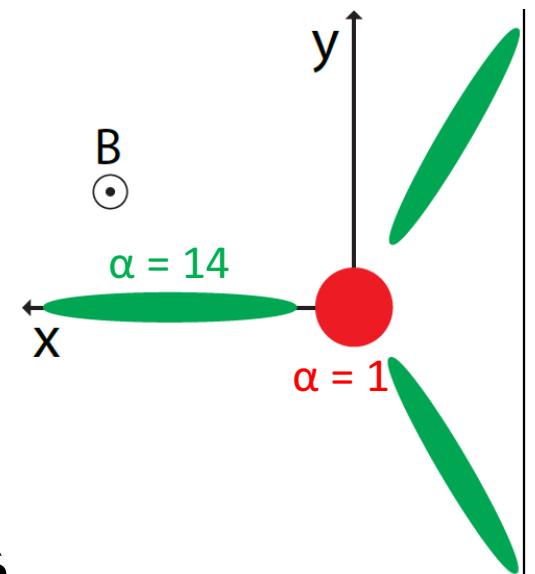
$$\hat{\sigma}_{e1} = \begin{pmatrix} \alpha^{-1}s_{xx} & s_{xy} \\ -s_{xy} & \alpha s_{xx} \end{pmatrix}$$

Adding three anisotropic pockets together...

One pocket conductivity:

$$\hat{\sigma}^{e1} = \begin{pmatrix} \tilde{\sigma}_{xx} & \tilde{\sigma}_{xy} \\ -\tilde{\sigma}_{xy} & \tilde{\sigma}_{yy} \end{pmatrix} = \begin{pmatrix} \alpha^{-1} s_{xx} & s_{xy} \\ -s_{xy} & \alpha s_{xx} \end{pmatrix}$$

$$\alpha = \sqrt{\frac{m_x}{m_y}}$$



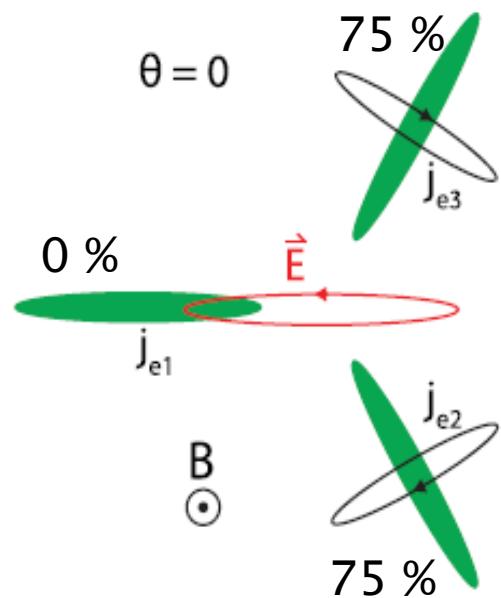
Add three pockets:

$$\hat{\sigma}^{tot} = \hat{\sigma}^{e1} + \hat{\sigma}^{e2} + \hat{\sigma}^{e3} = \hat{\sigma}^{e1} + \hat{R} \hat{\sigma}^{e1} \hat{R}^{-1} + \hat{R}^{-1} \hat{\sigma}^{e1} \hat{R}$$

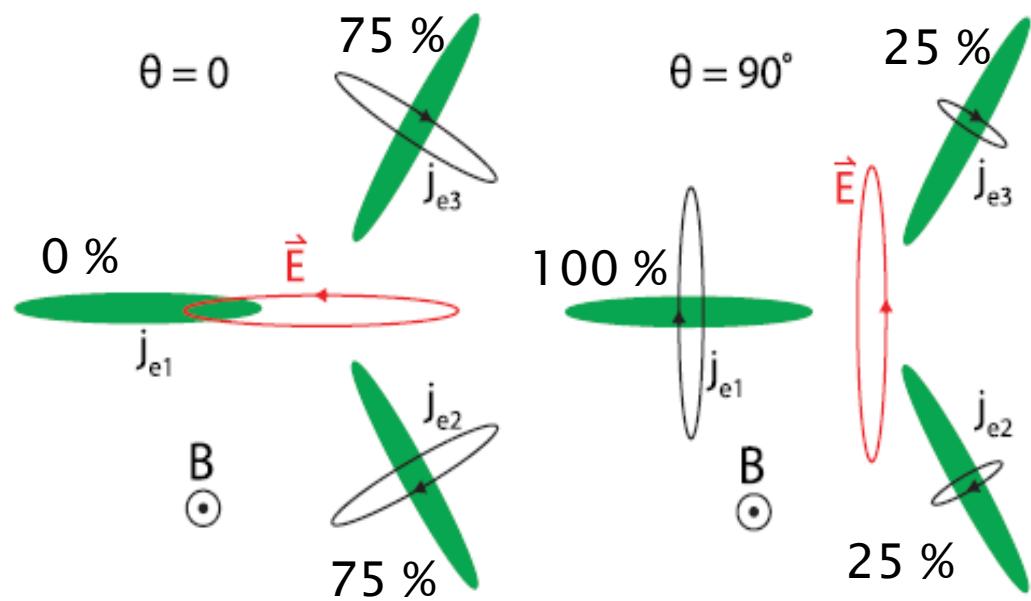
$$MCD = \frac{\sigma_e^+ - \sigma_e^-}{\sigma_e^+ + \sigma_e^-} = \frac{2}{\alpha + \alpha^{-1}} \approx 13.8\%$$

Agrees perfectly with experiment !

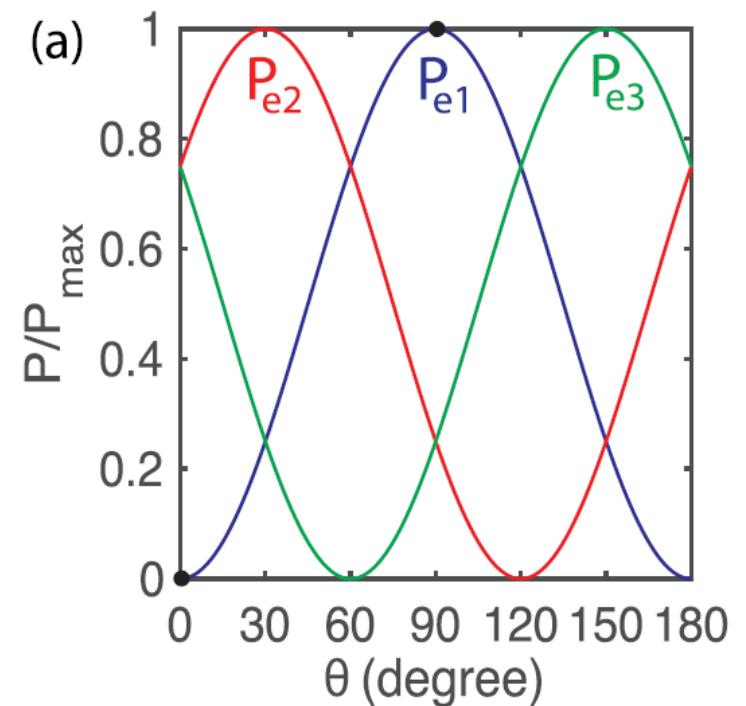
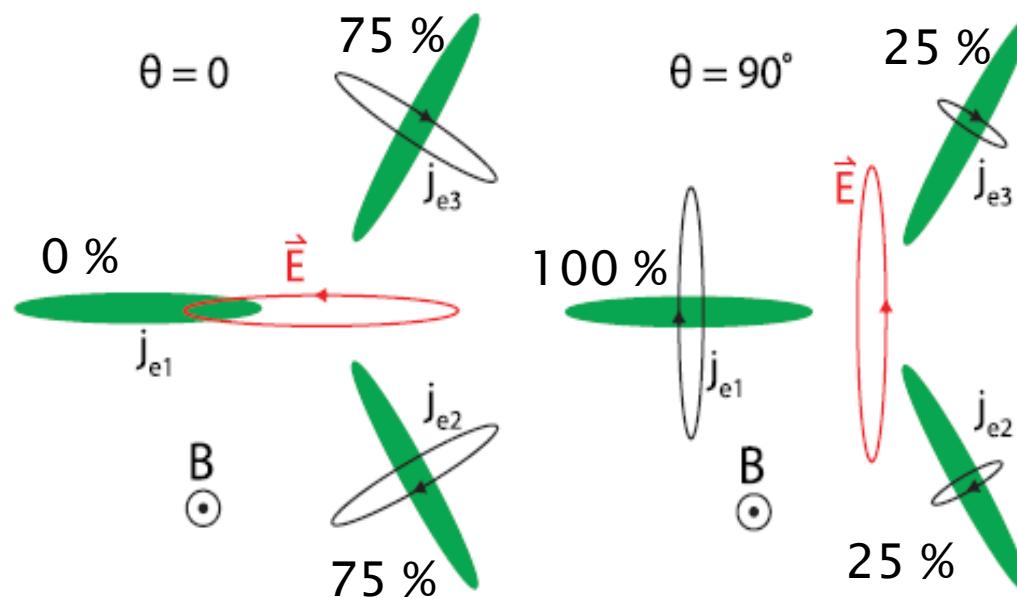
Valley-selective absorption in bismuth



Valley-selective absorption in bismuth

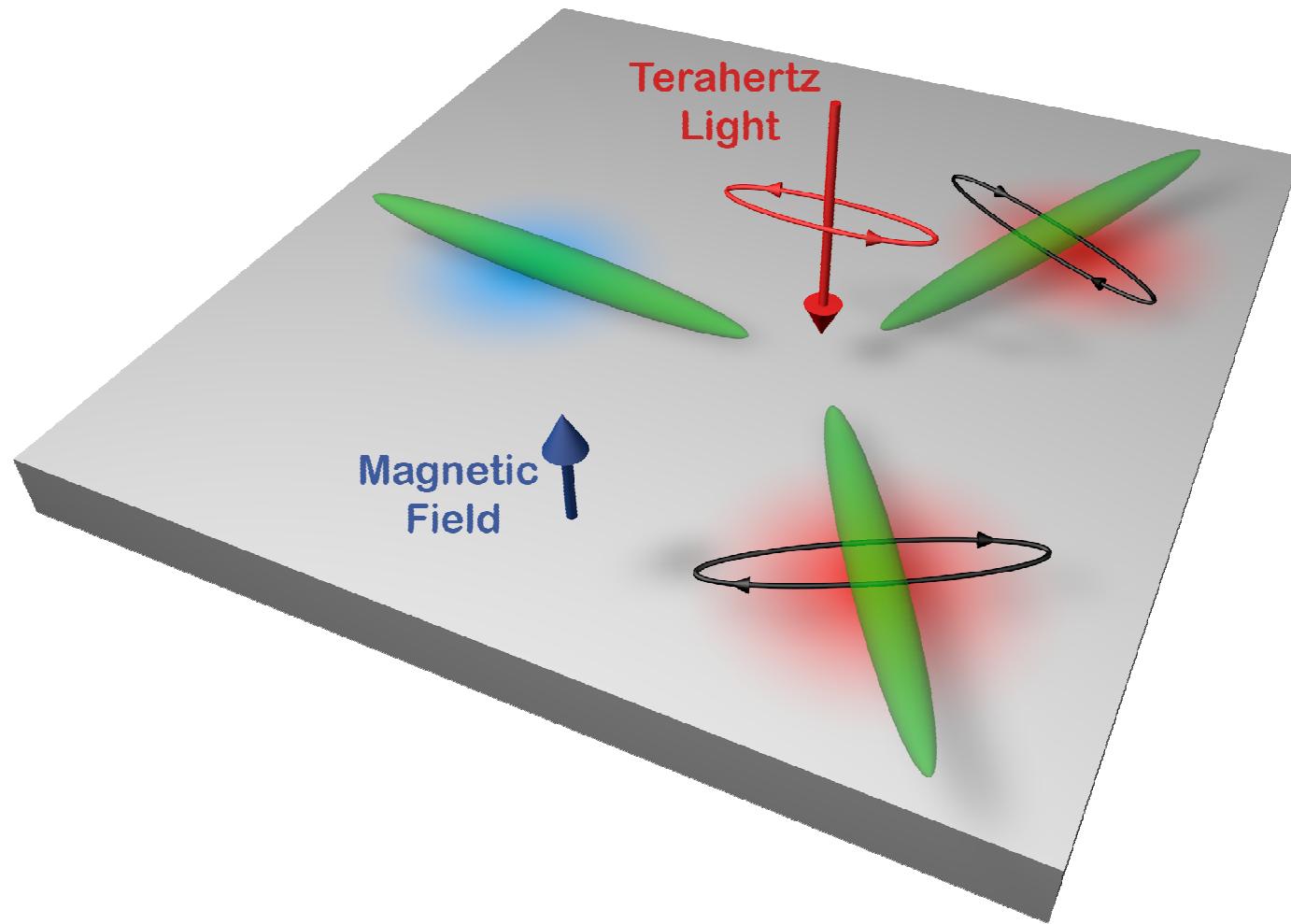


Valley-selective absorption in bismuth



- Elliptical light absorbed differently in different valleys
- Valley are selected by the azimuth angle

Valley-selective absorption in bismuth

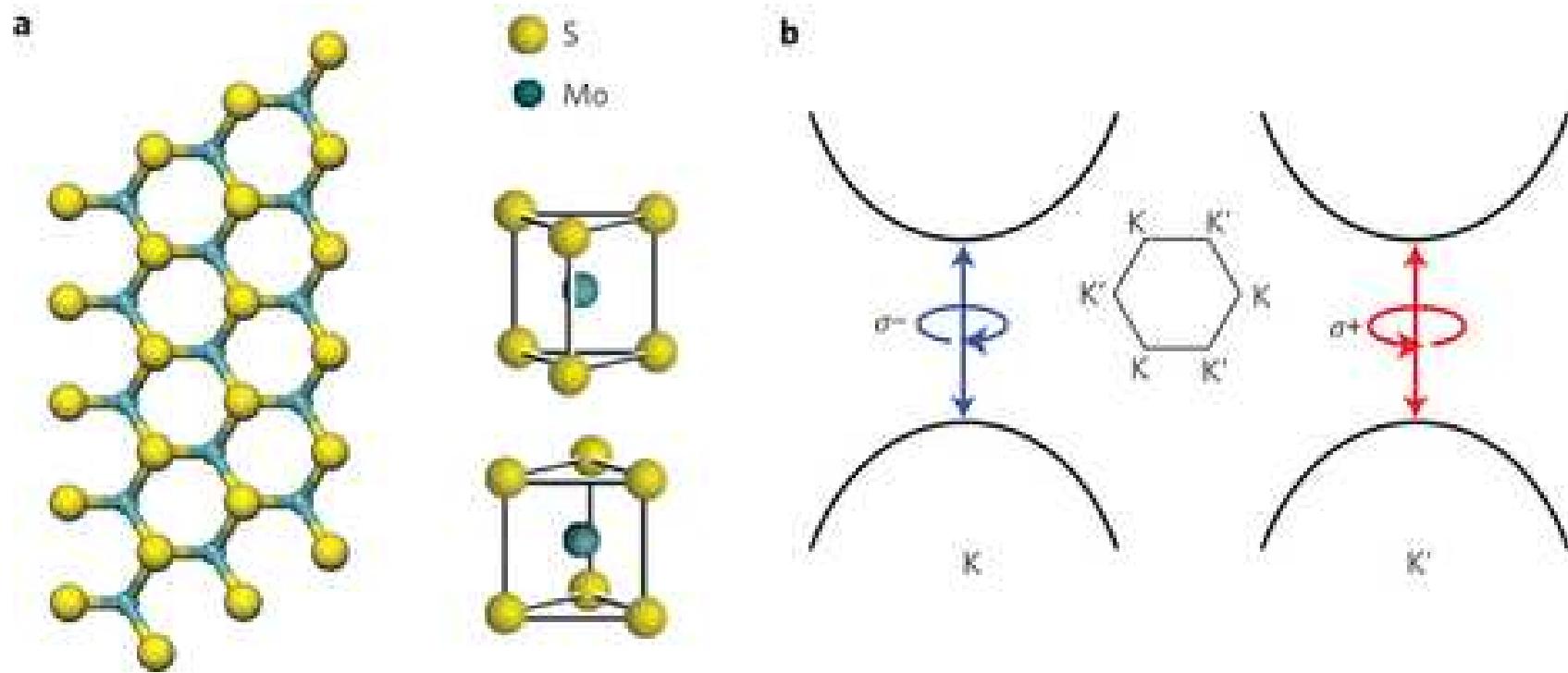


Mean-free path up to millimeters (at 5 K)

A new playground for valleytronics ?

Valley-selective absorption in TMDs

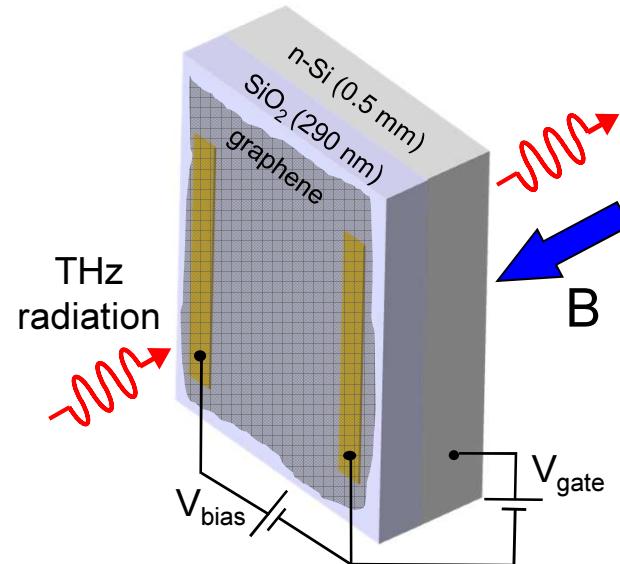
- Spin-polarized valence band (due to SO interaction)
- Valley-selective excitation with circularly polarised light



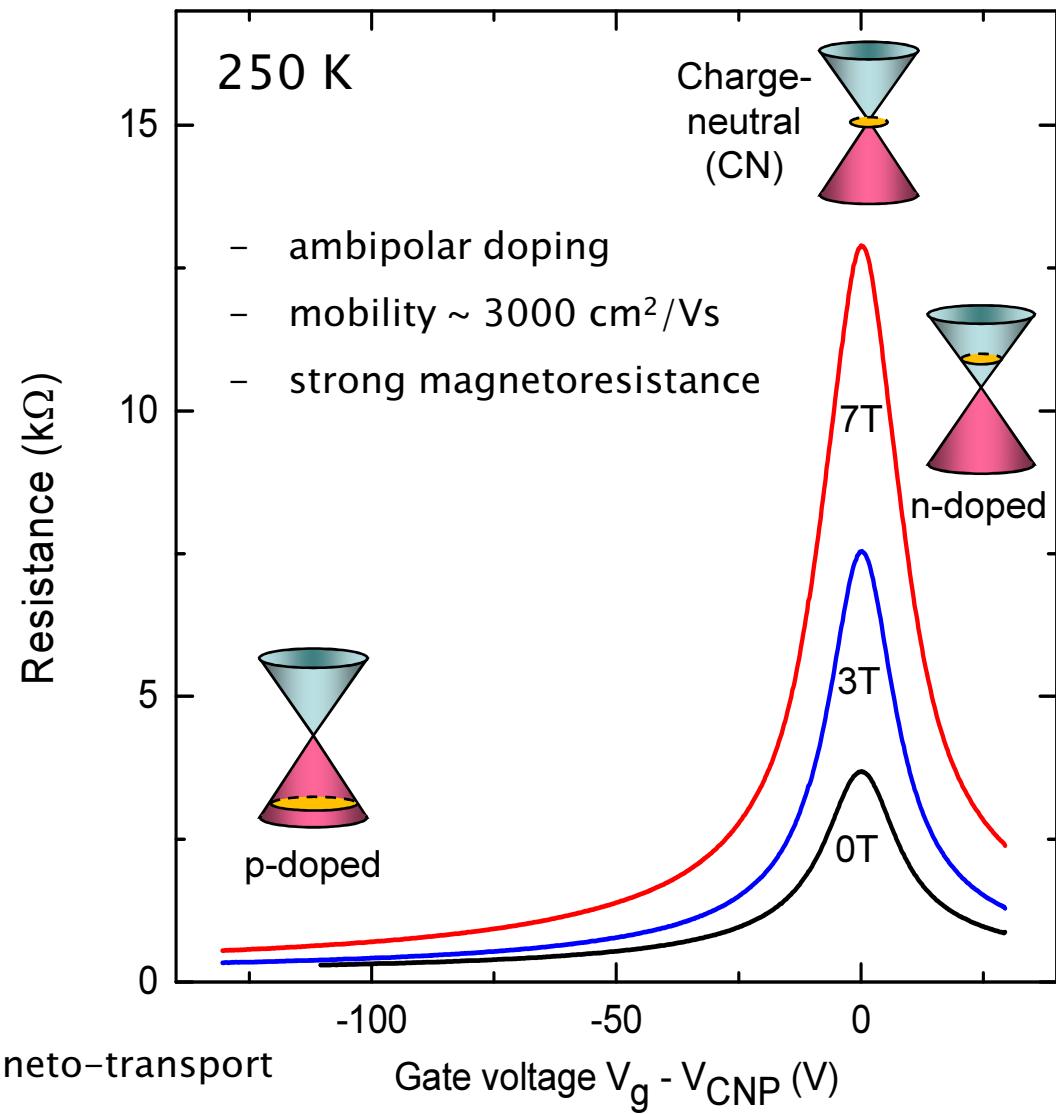
Outline

- **Atomistic simulation of adsorption and desorption processes connected to charge transfer phenomena**
- **Electrically controlled terahertz magneto-optical phenomena in graphene**

Graphene field-effect transistor (g-FET) for THz wave manipulation

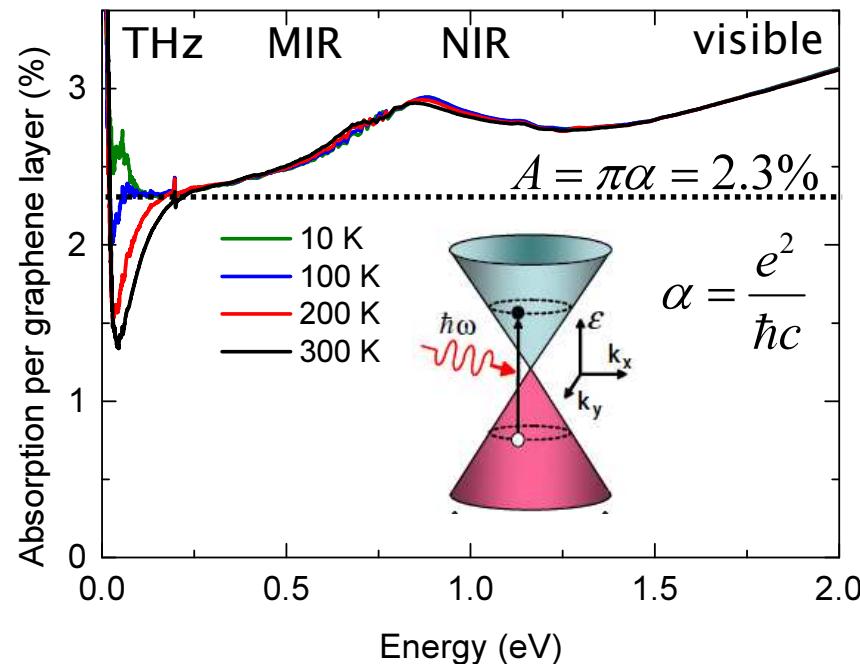


- large area needed for THz
- substrate SiO_2 (300 nm)/Si
- Low-doped Si for THz transparency
- CVD graphene transferred from Cu
- evaporated Au/Ti contacts
- annealed by high current in vacuum
- simultaneous magneto-optics and magneto-transport



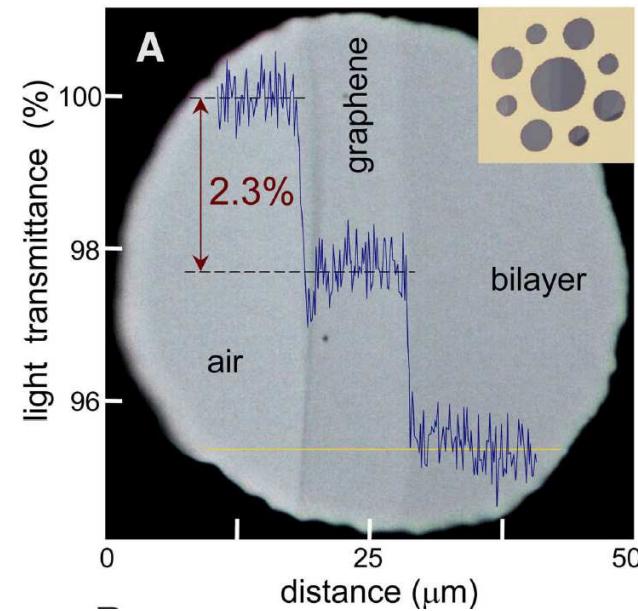
Optical absorption in graphene

Graphite (HOPG)



A. B. Kuzmenko et al., Phys. Rev. Lett. (2008)

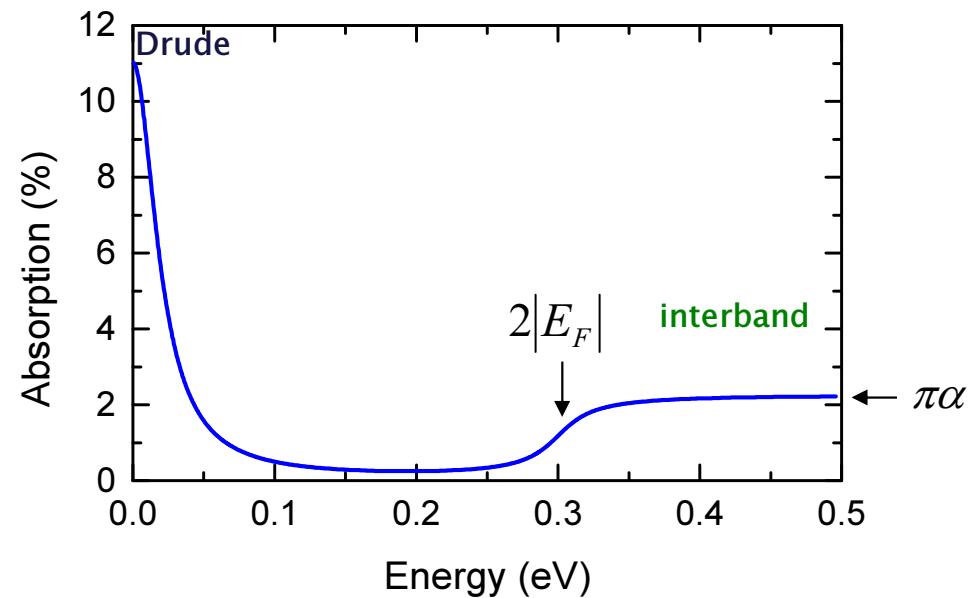
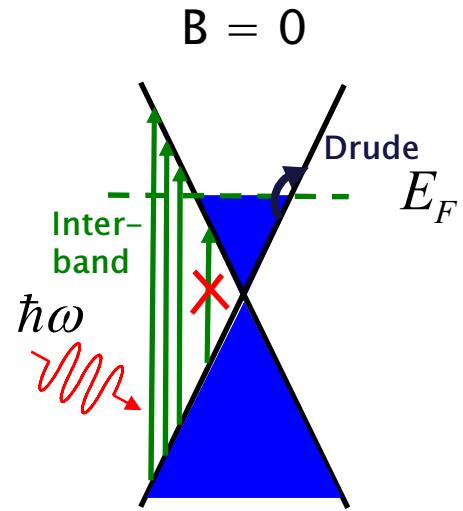
Graphene membrane (visible)



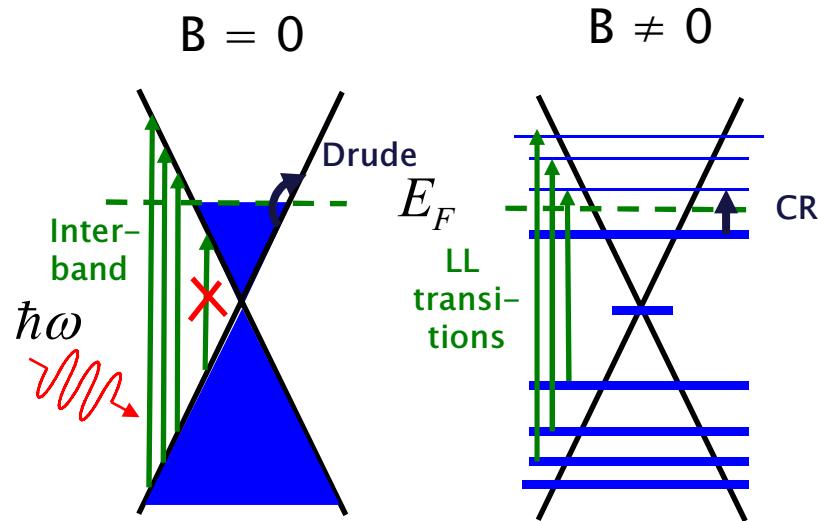
A.A. Nair et al., Science (2008)

Absorption in graphene is ‘universal’: 2.3%
but in the THz range it is much higher!!!
(thanks to Drude carriers)

Magneto-optical absorption of graphene: theory



Magneto-optical absorption of graphene: theory



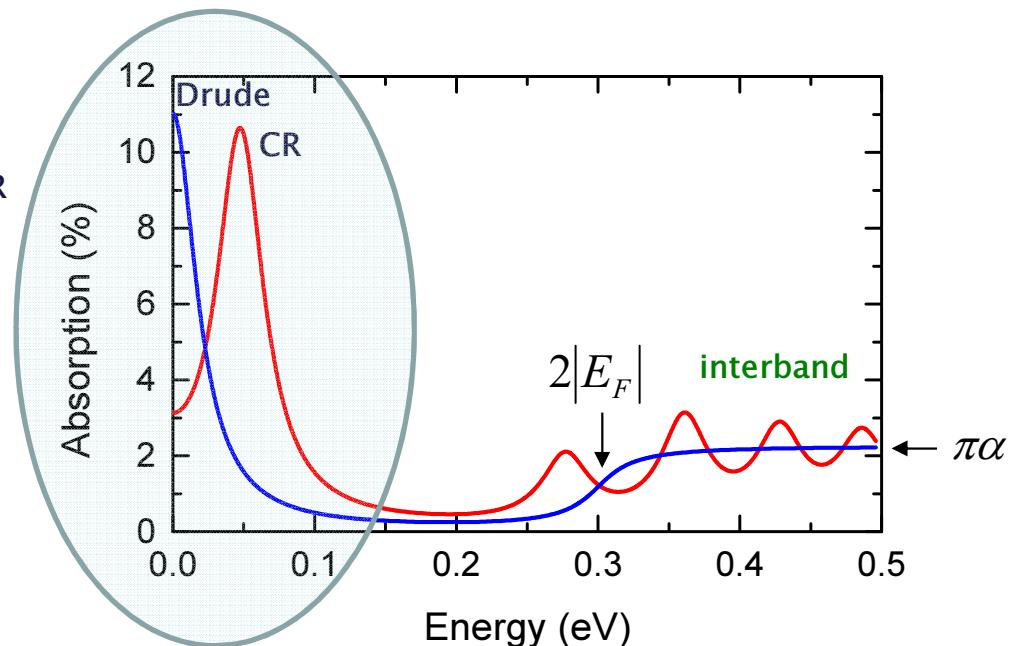
At high doping: 'classical' cyclotron resonance (CR)

$$\sigma_{\pm}(\omega, B) = \frac{D}{\pi} \cdot \frac{i}{\omega \mp \omega_c(B) + i/\tau}$$

$$D = \frac{\pi n e^2}{m^*} \quad \text{- Drude weight}$$

τ - scattering time

$$\omega_c = \frac{eB}{m^*} \quad \text{- cyclotron frequency}$$



$$\text{Dirac fermions*}: m^* = \frac{\hbar}{v_F} \sqrt{\pi n}$$

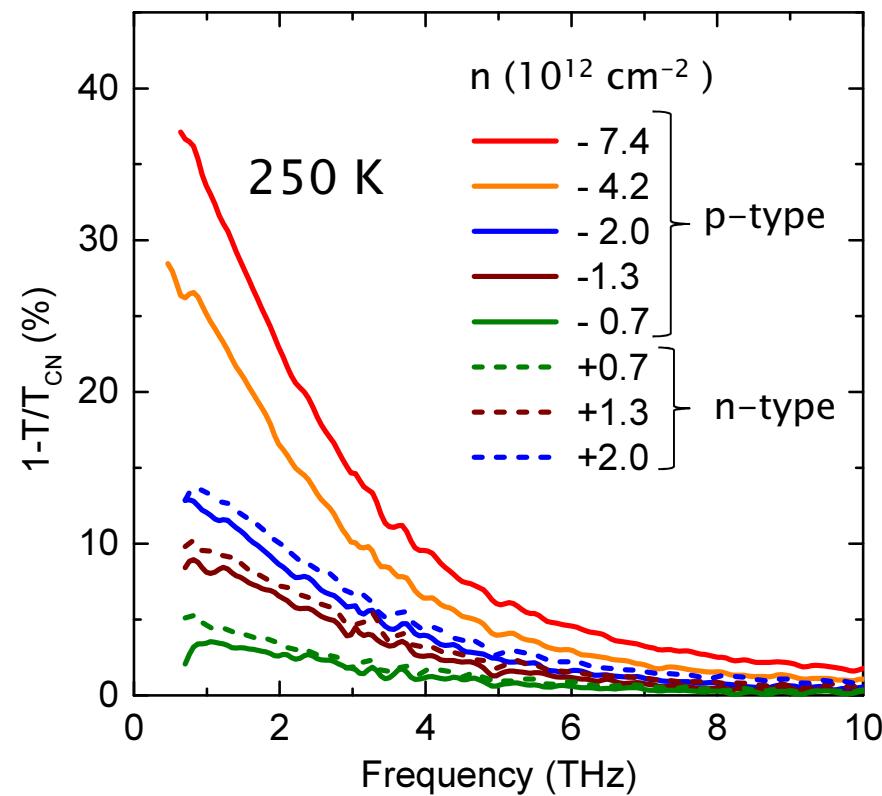
$$D = \frac{e^2}{\hbar} v_F \sqrt{\pi n} \quad \omega_c = \frac{eB}{\hbar} \frac{v_F}{\sqrt{\pi n}} \text{sign}(n)$$

Different from 2DEGs !

Ando (2002), Peres et al (2006)
 Abergel & Falko (2007), Gusynin et al (2007)
 Witowski (2010), Crassee (2011)

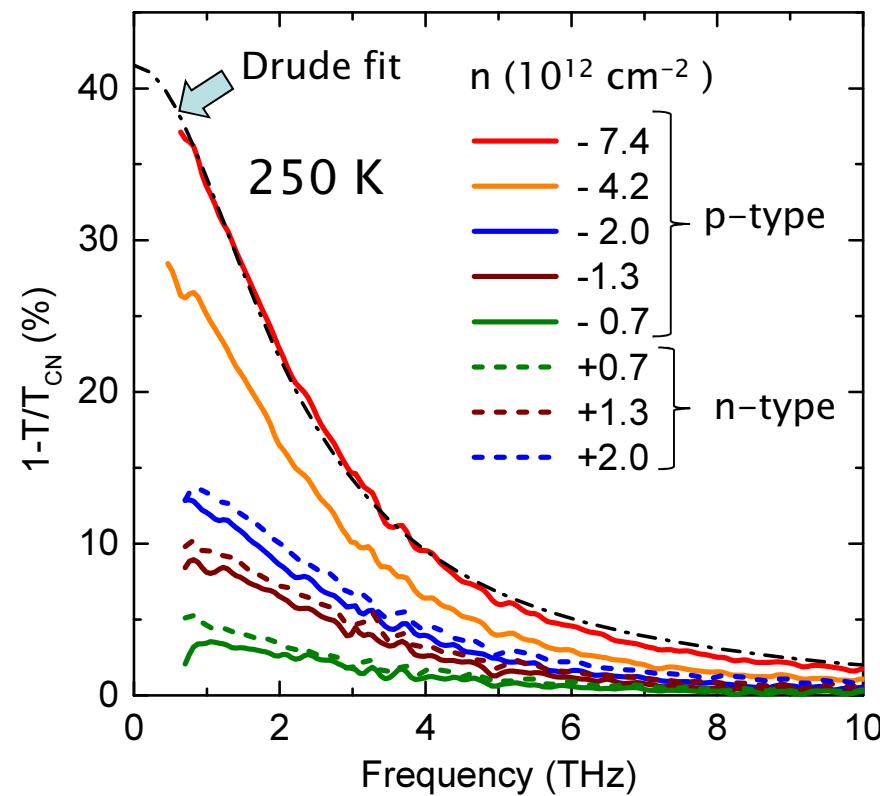
*interactions not included

Doping-dependent THz absorption in zero field



- ~40% absorption (<1THz)
- electron-hole symmetry

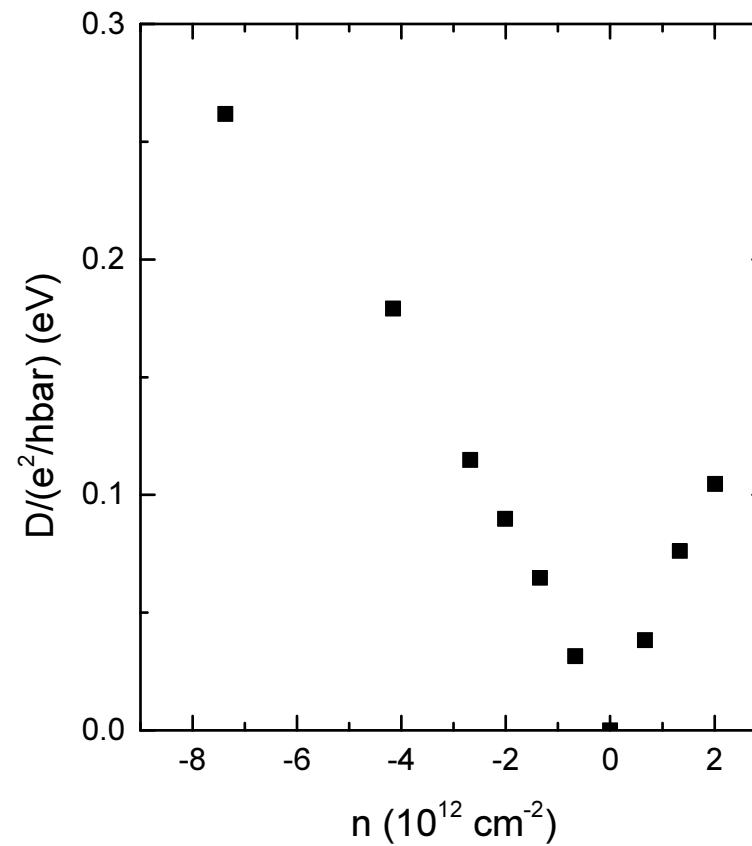
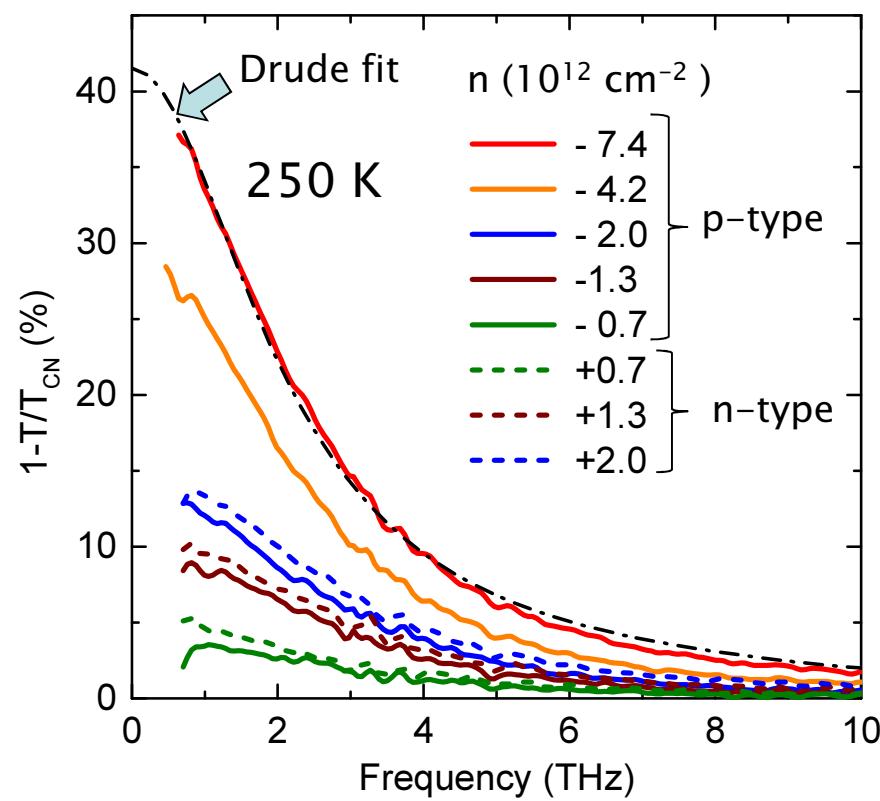
Doping-dependent THz absorption in zero field



- ~40% absorption (<1THz)
- electron-hole symmetry
- Drude model works well

$$\sigma(\omega) = \frac{D}{\pi} \cdot \frac{i}{\omega + i/\tau}$$

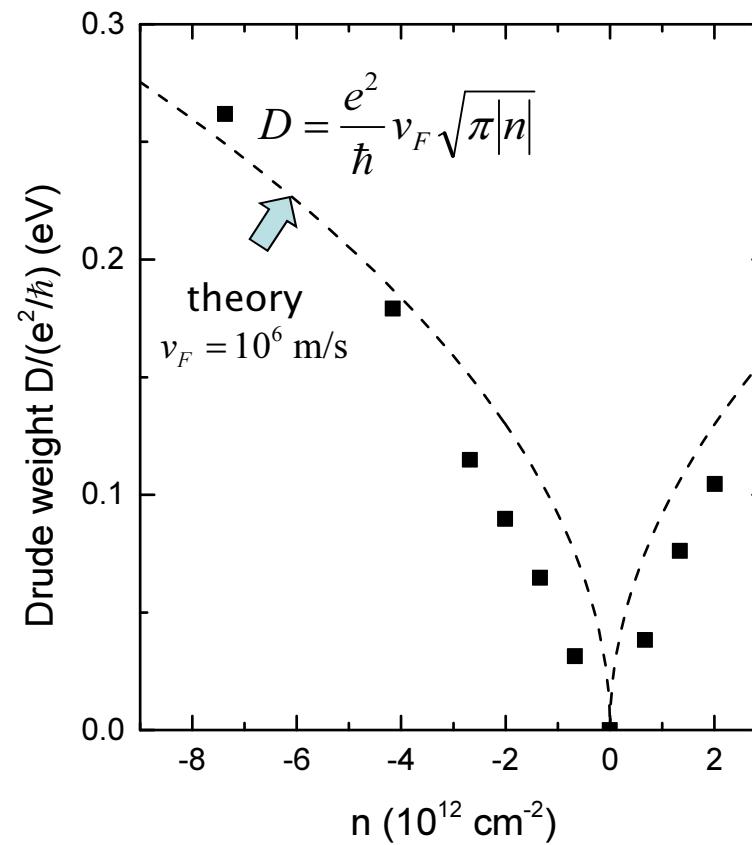
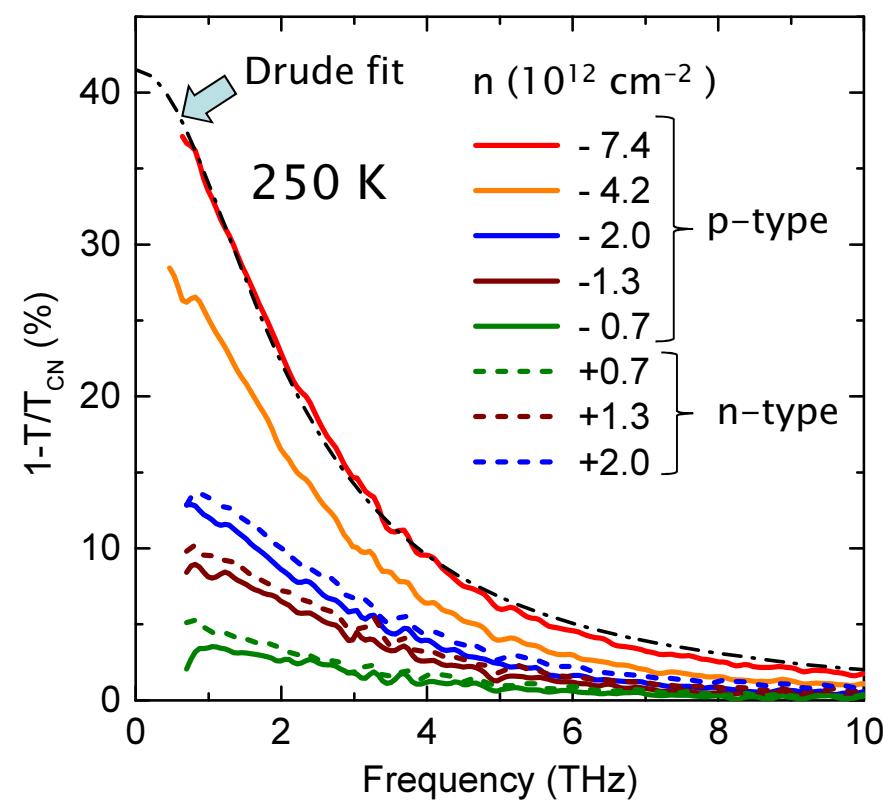
Doping-dependent THz absorption in zero field



- ~40% absorption (<1THz)
- electron-hole symmetry
- Drude model works well

$$\sigma(\omega) = \frac{D}{\pi} \cdot \frac{i}{\omega + i/\tau}$$

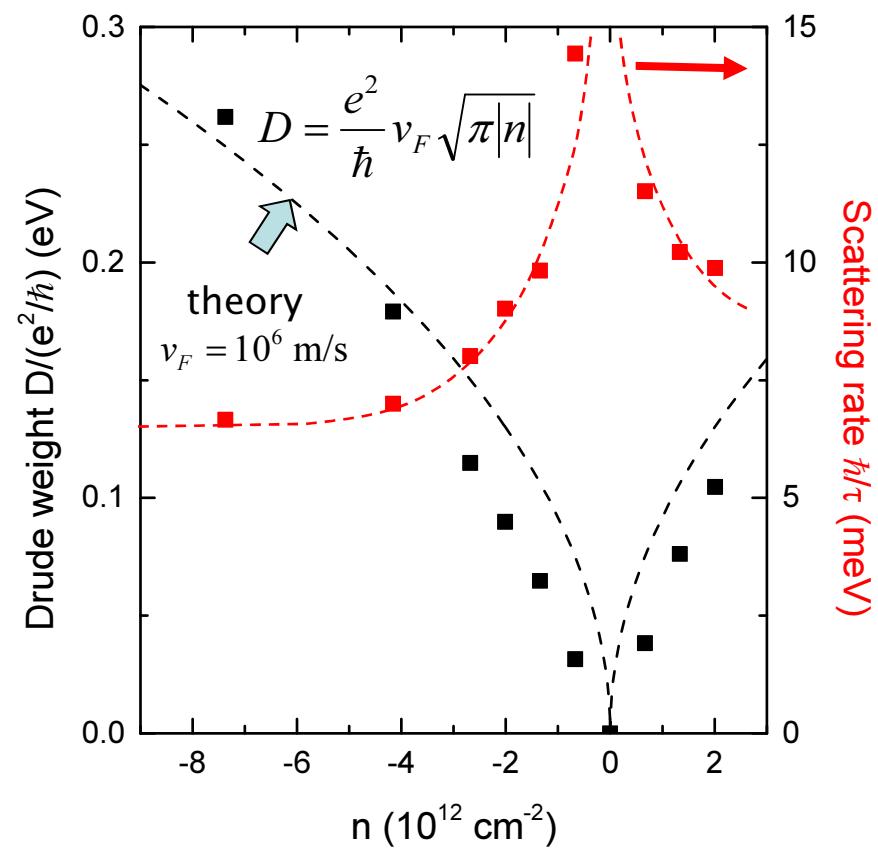
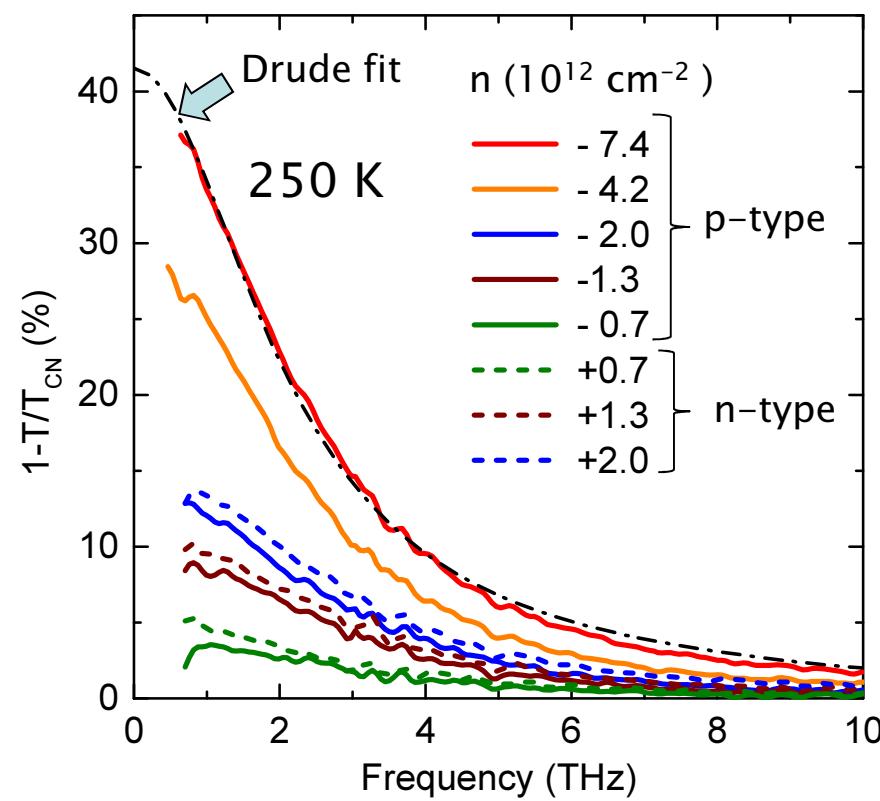
Doping-dependent THz absorption in zero field



- ~40% absorption (<1THz)
- electron-hole symmetry
- Drude model works well

$$\sigma(\omega) = \frac{D}{\pi} \cdot \frac{i}{\omega + i/\tau}$$

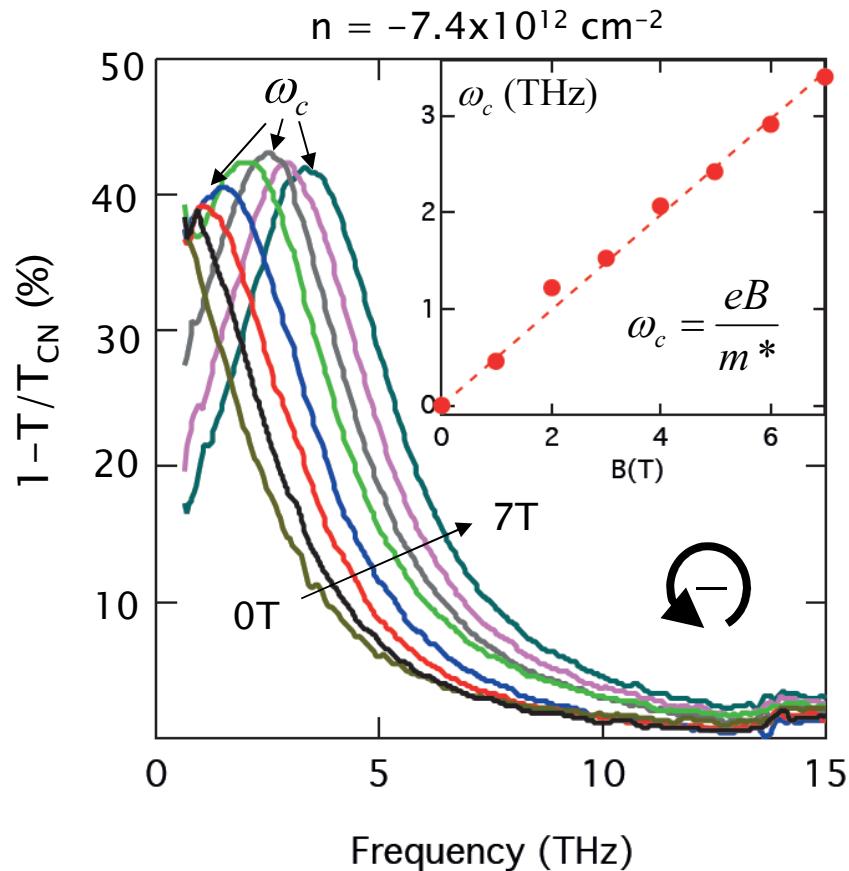
Doping-dependent THz absorption in zero field



- ~40% absorption (<1 THz)
- electron-hole symmetry
- Drude model works well
- Scattering by charged impurities (decreases with n)

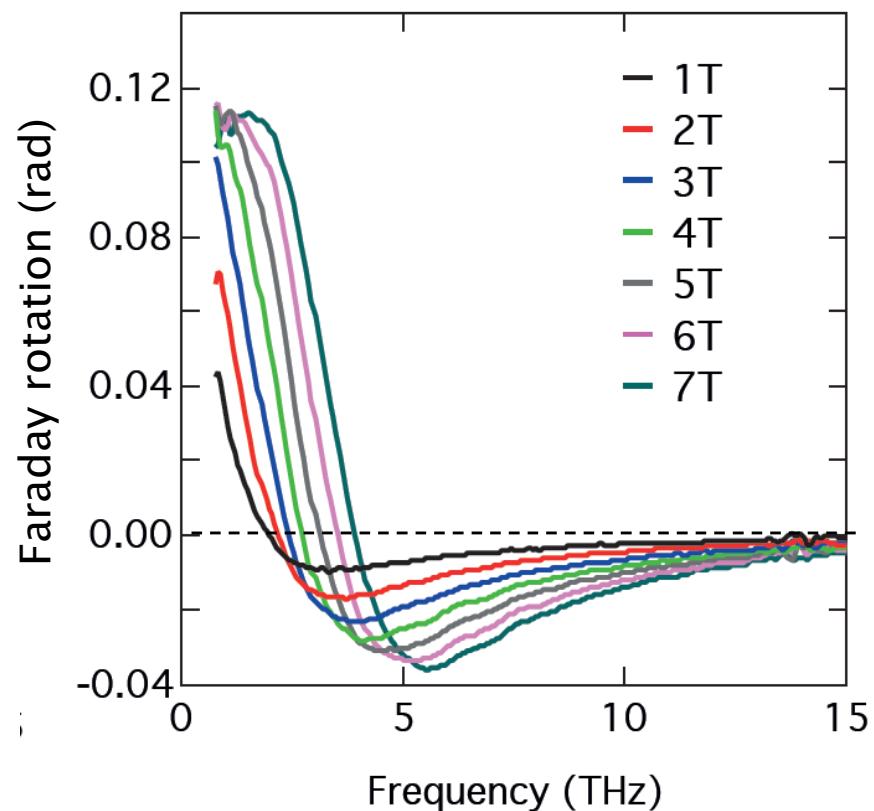
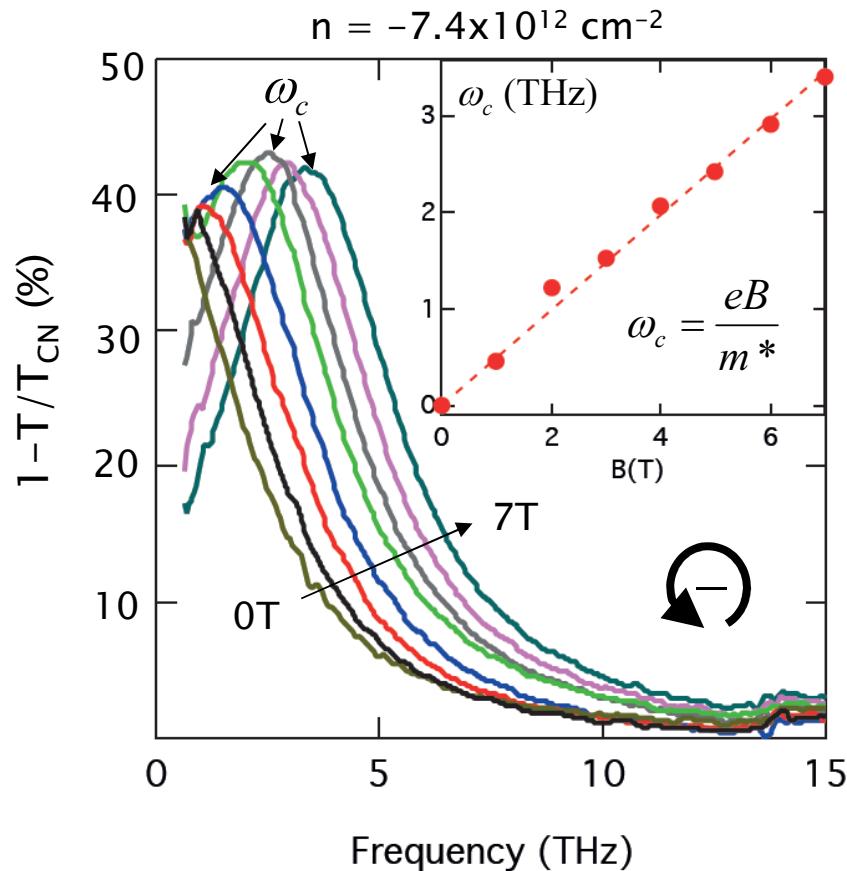
$$\sigma(\omega) = \frac{D}{\pi} \cdot \frac{i}{\omega + i/\tau}$$

B-field dependence of THz effects (high doping)



- Absorption >40% at 3 THz
- Cyclotron frequency is B-linear

B-field dependence of THz effects (high doping)

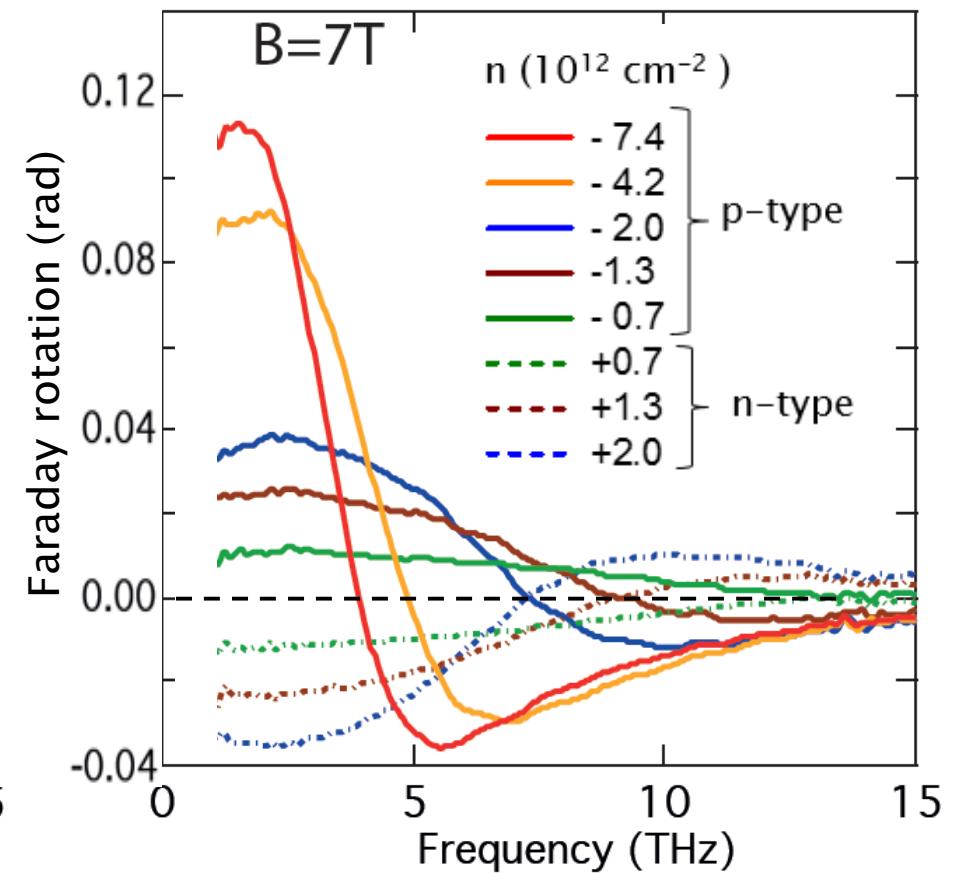
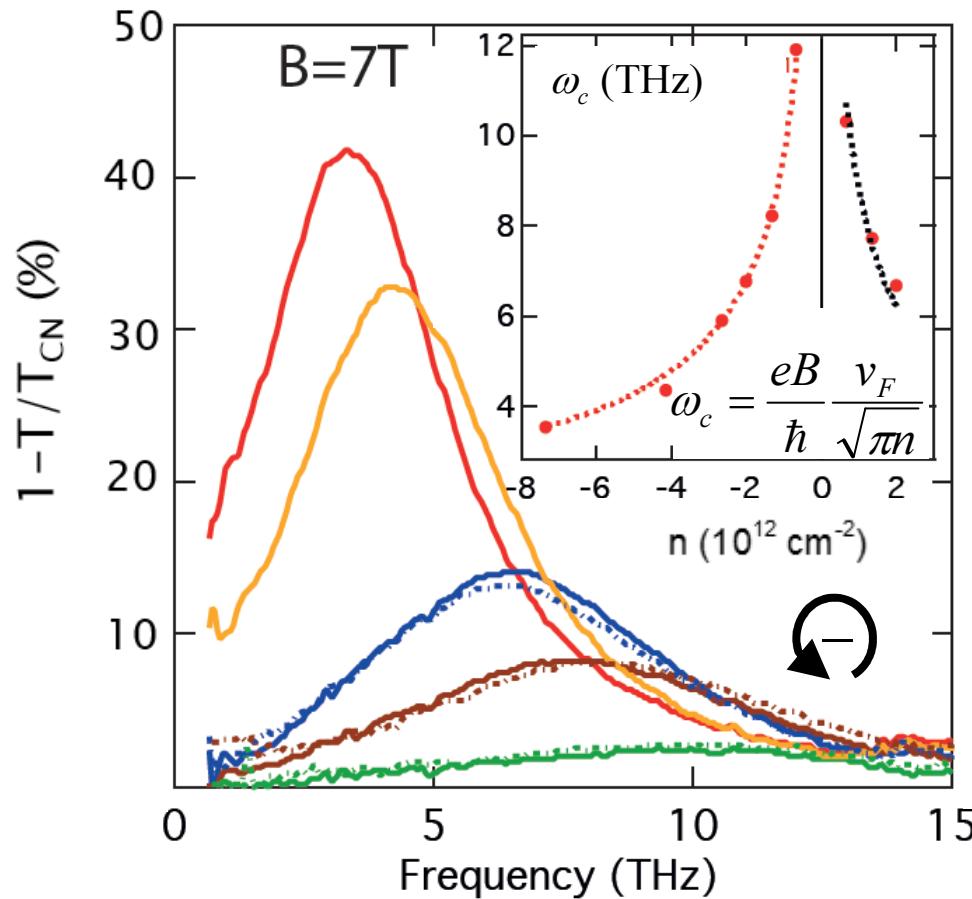


- Absorption $>40\%$ at 3 THz
- Cyclotron frequency is B-linear

- Faraday rotation $\theta_F > 0.1$ rad (6 deg)

Similar to epitaxial graphene on SiC:
I. Crassee *et al.* *Nature Phys.* 7, 48 (2011)

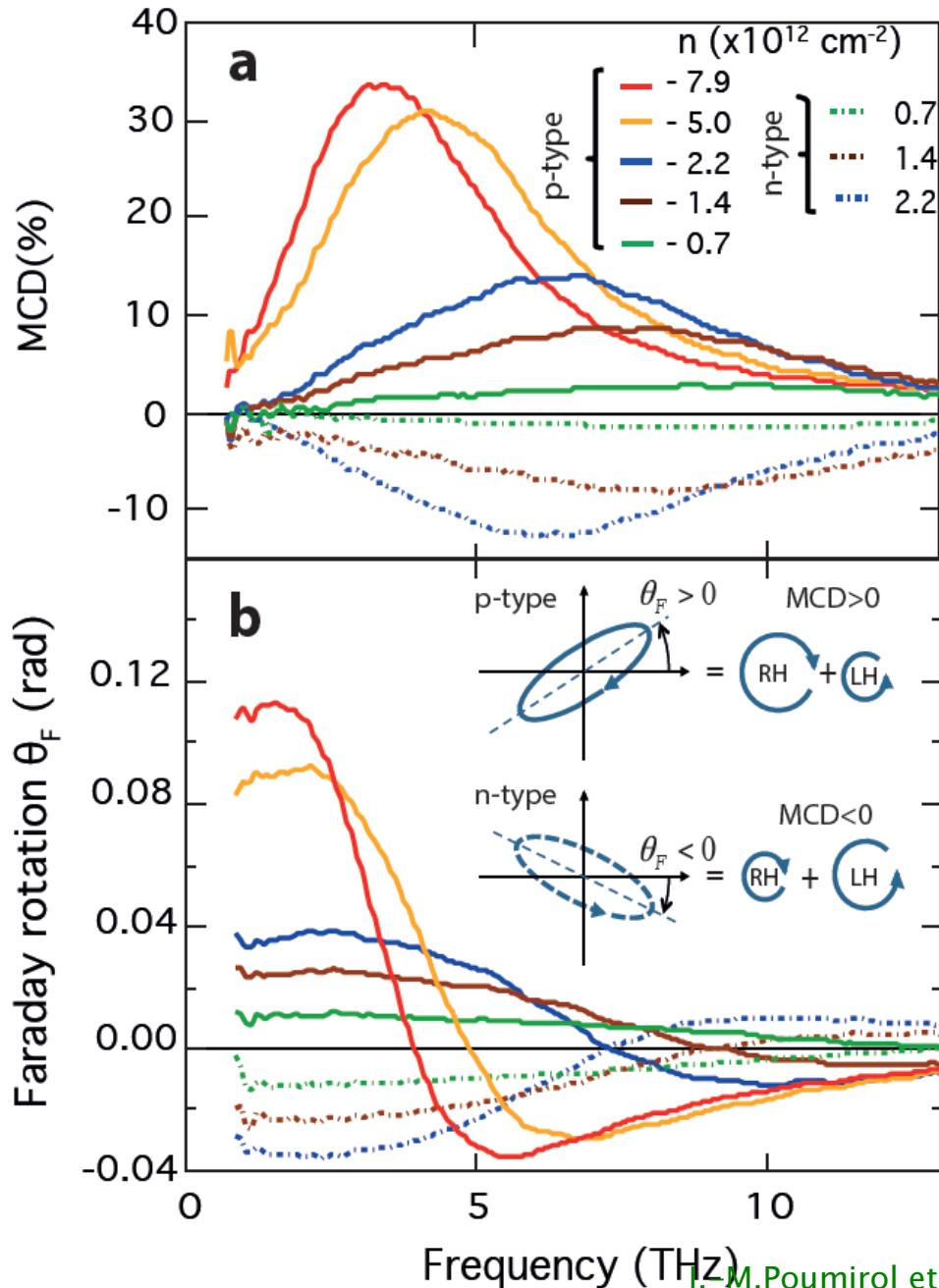
Doping dependence of MO THz effects



- Cyclotron frequency $\omega_c \sim n^{-1/2}$
- $\omega_c > 10 \text{ THz}$ can be reached !

Drastically different from 2DEGs!

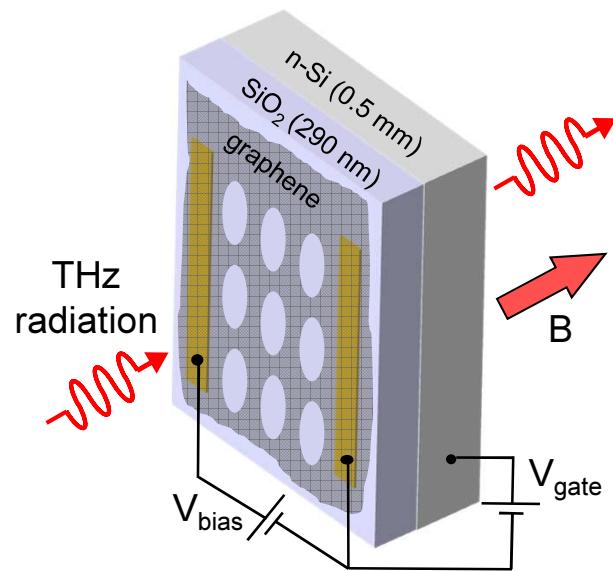
Electric control of MCD and Faraday rotation



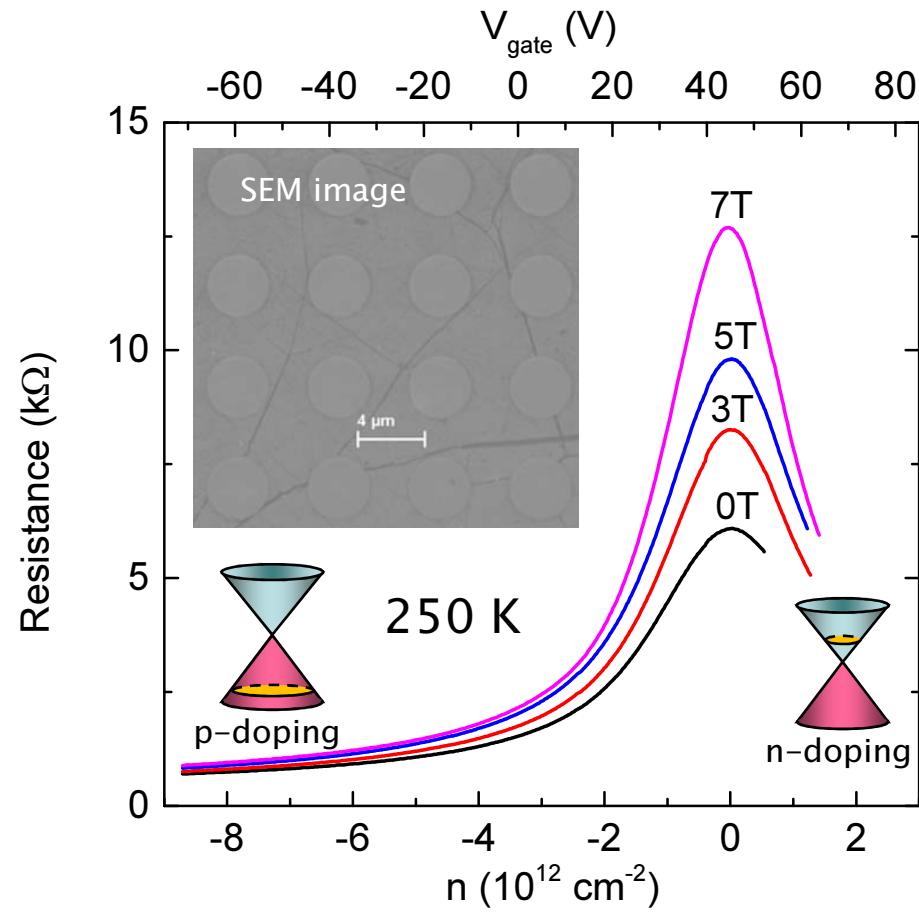
- Magnetic circular dichroism and Faraday rotation can be inverted electrostatically !
- Electric control of a magnetic effect !
- Potentially new MO device functionalities !

Graphene antidots: fabrication and transport

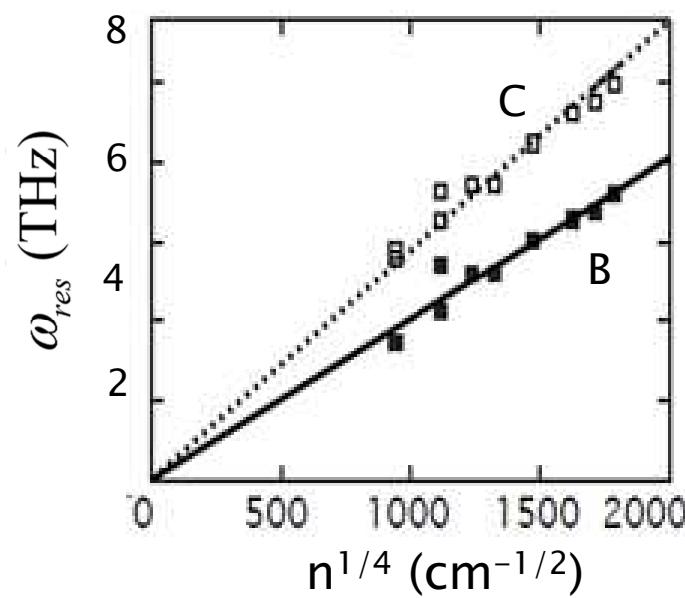
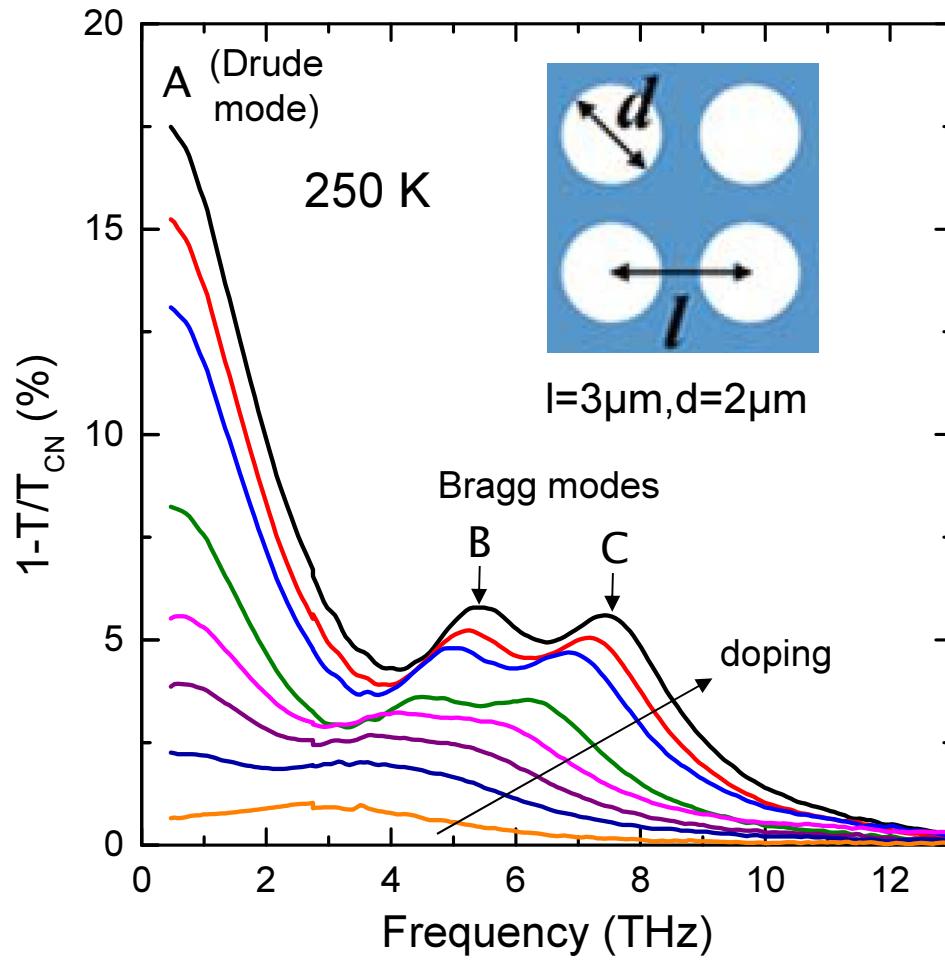
Square array of
micron-size holes (antidots)



patterned by deep-UV
photolithography
and O_2 -plasma etching



Graphene antidots: zero-field THz absorption



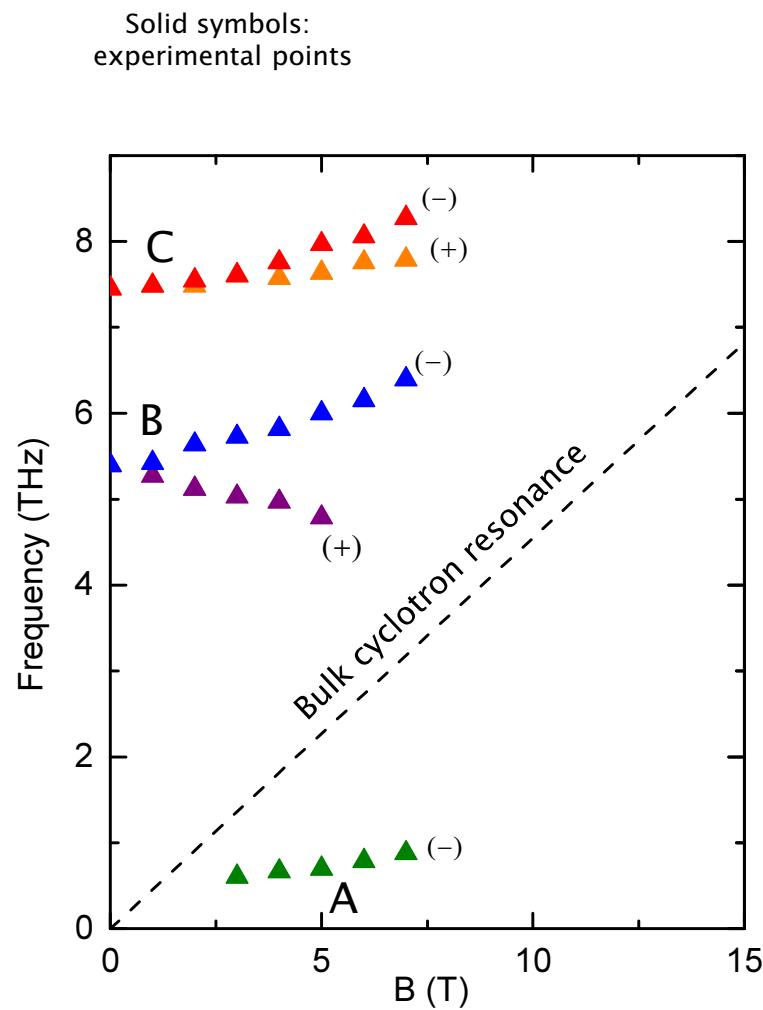
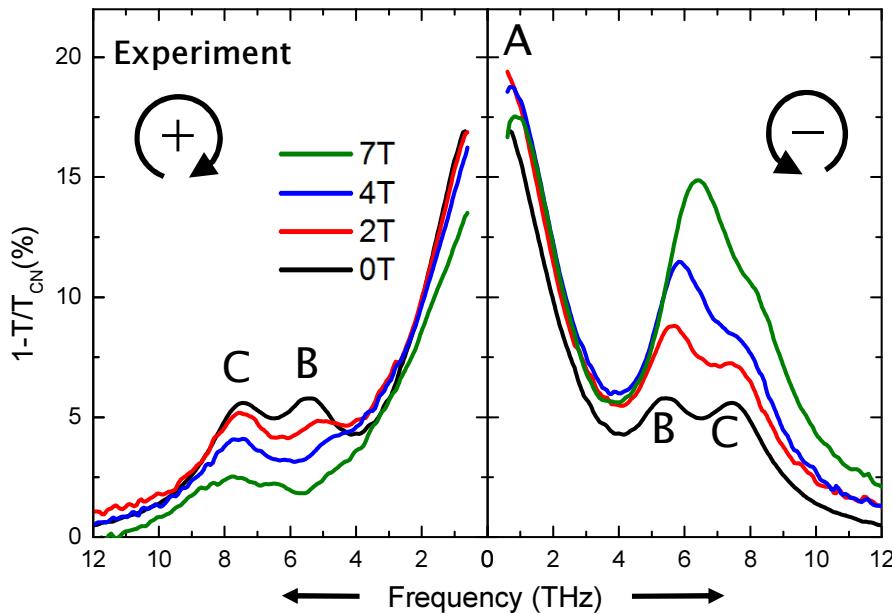
2D plasmon dispersion:
$$\omega_{pl}(n, q) = \left(\frac{4\pi n e^2 q}{m(\epsilon_{sub} + 1)} \right)^{1/2}$$

In graphene
 $m \propto n^{1/2}$ $\Rightarrow \omega_{pl}(n, q) \propto n^{1/4} q^{1/2}$

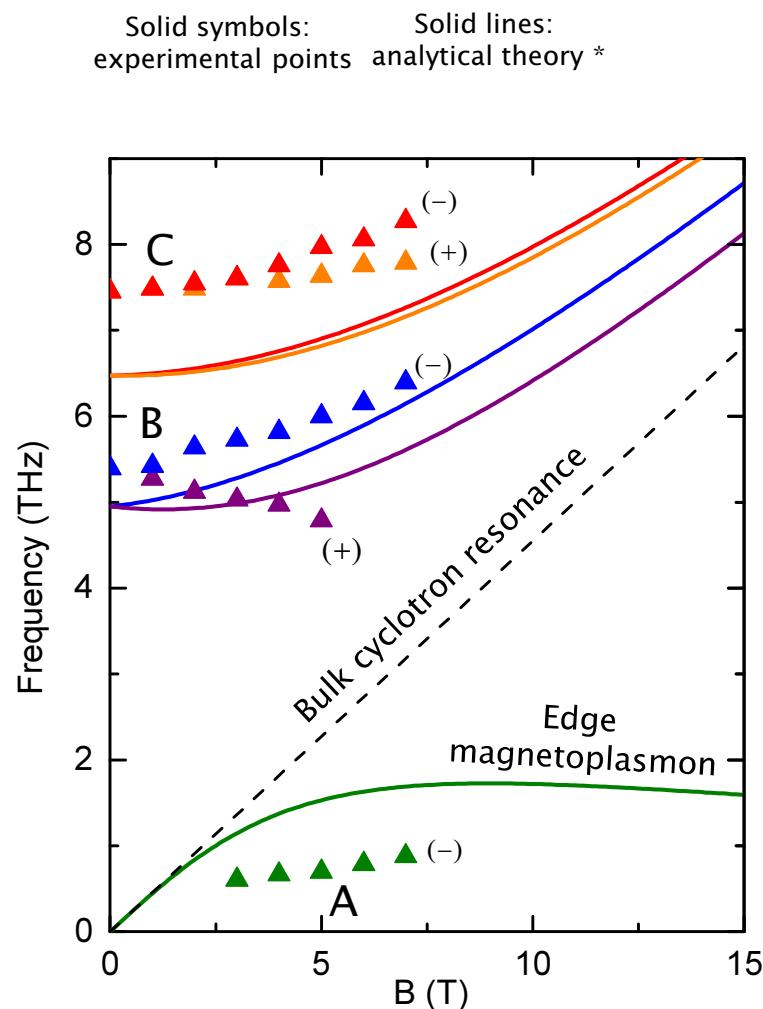
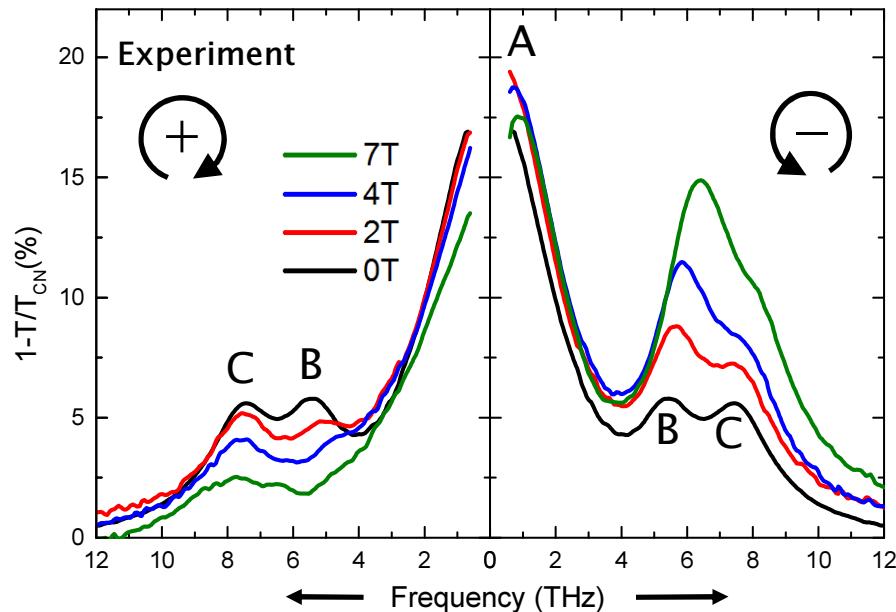
P. Q. Liu et al., Optica 2, 135 (2015)

J.-M. Poumirol et al., Nature Comm. (2017) DOI: 10.1038/ncomms14626

Graphene antidots: THz magneto-absorption

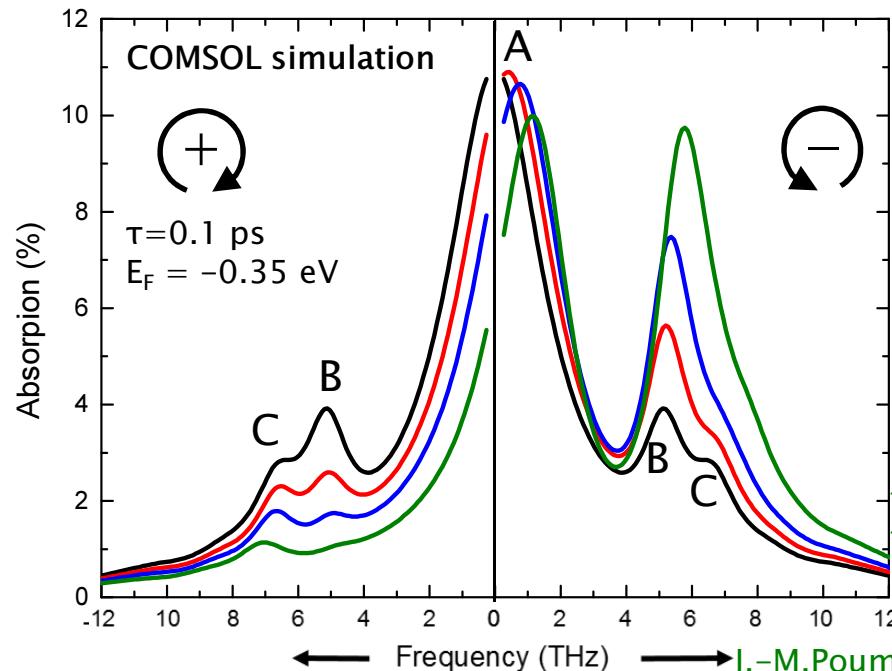
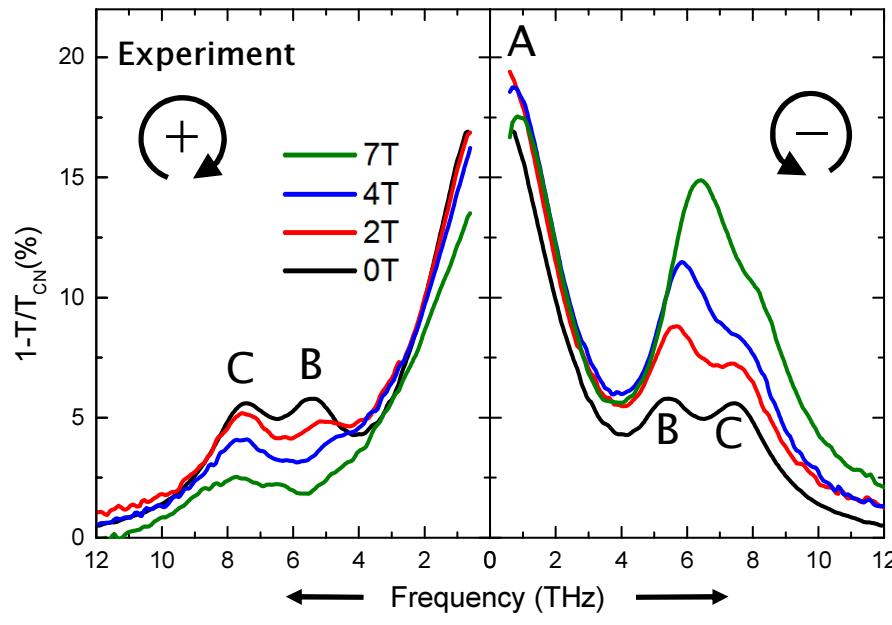


Graphene antidots: THz magneto-absorption

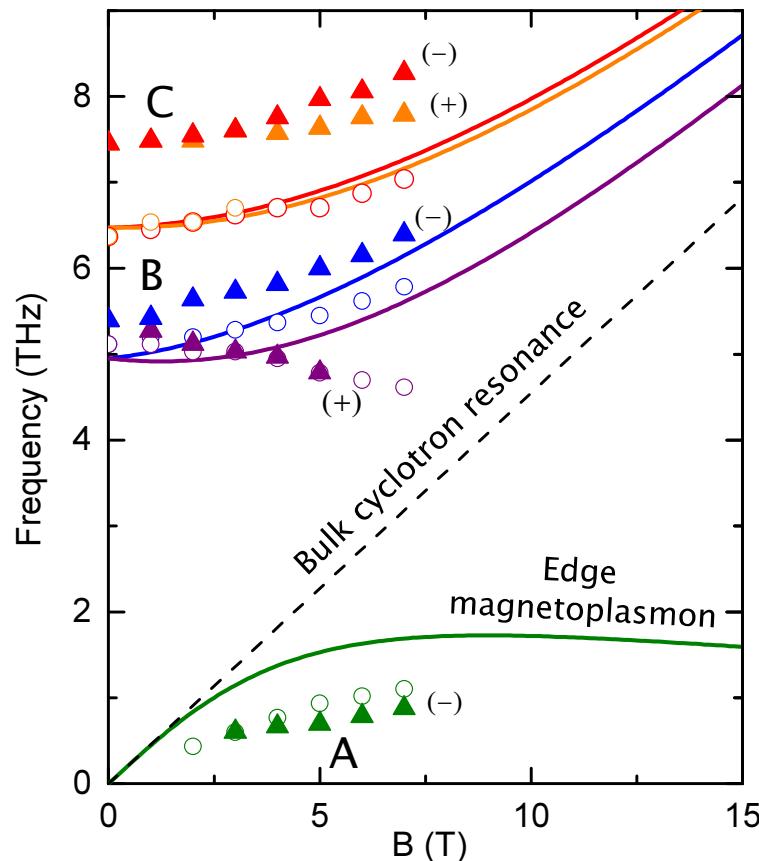


*S.A.Mikhailov and V.A. Volkov, Phys. Rev. B 52, 17260 (1995)
*S.A.Mikhailov, Phys. Rev. B 54, 14293 (1996)

Graphene antidots: THz magneto-absorption

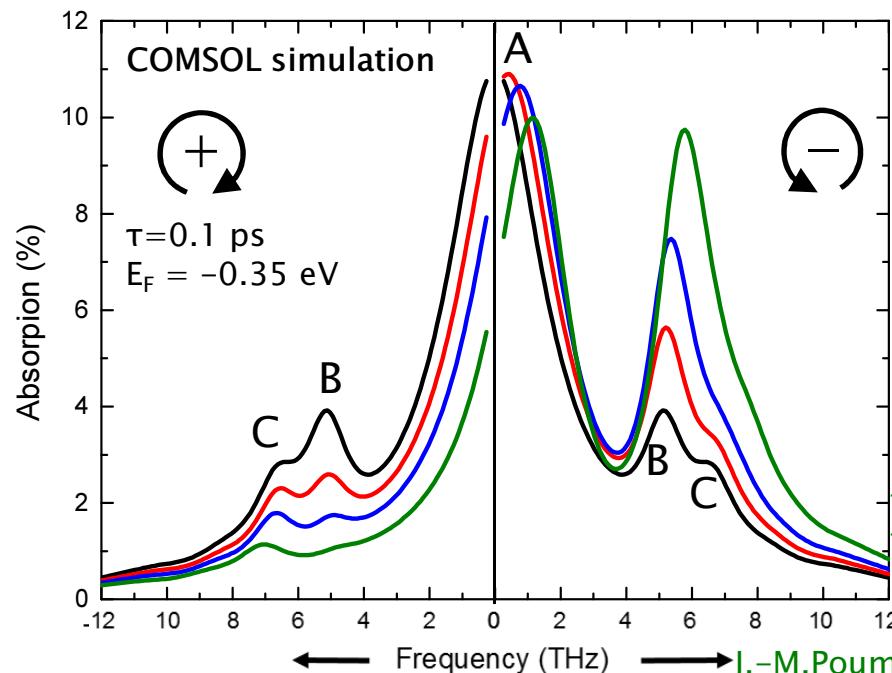
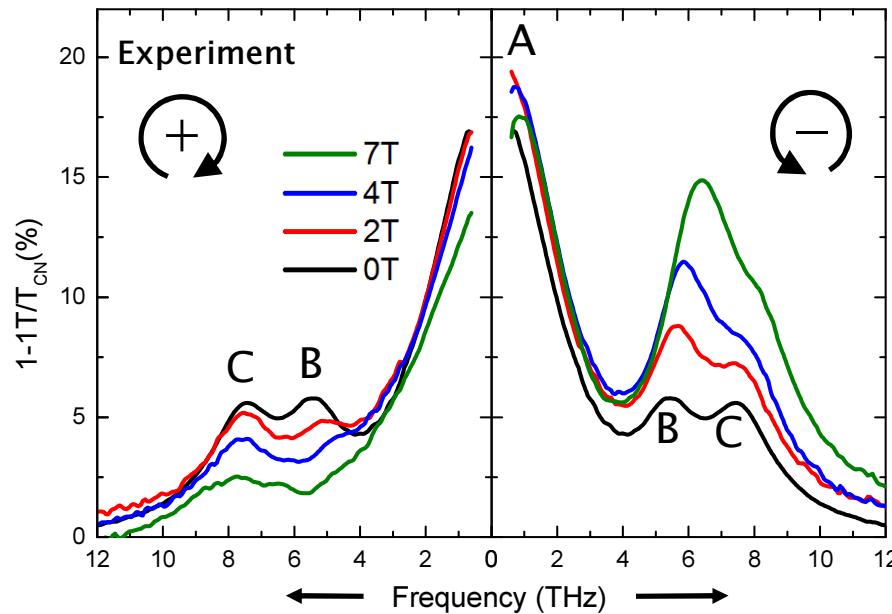


Solid symbols: experimental points
Solid lines: analytical theory *
Open circles: COMSOL simulation

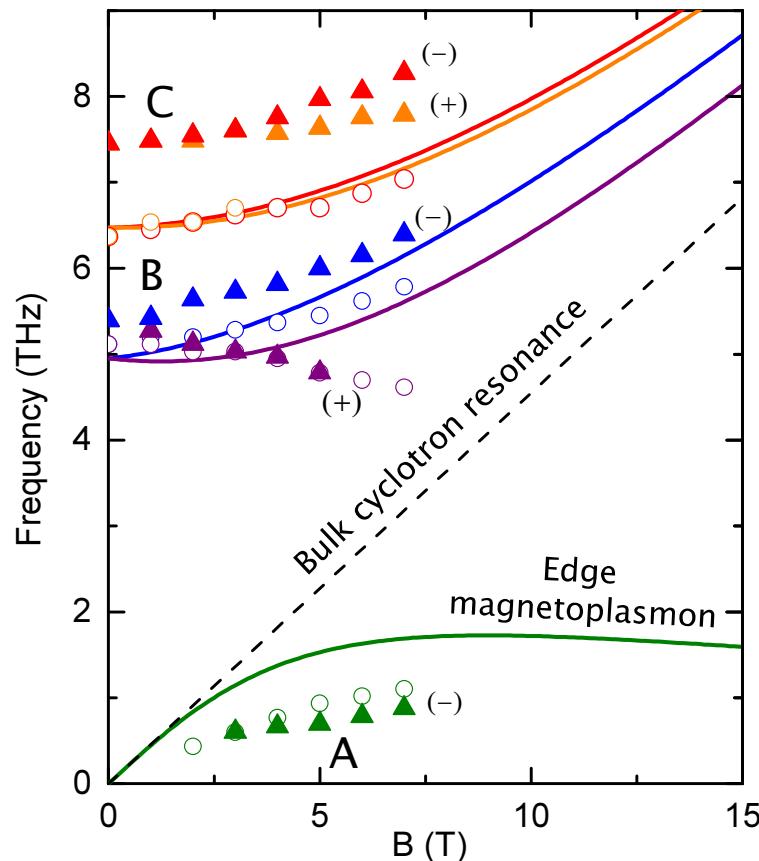


*S.A.Mikhailov and V.A. Volkov, Phys. Rev. B 52, 17260 (1995)
*S.A.Mikhailov, Phys. Rev. B 54, 14293 (1996)

Graphene antidots: THz magneto-absorption

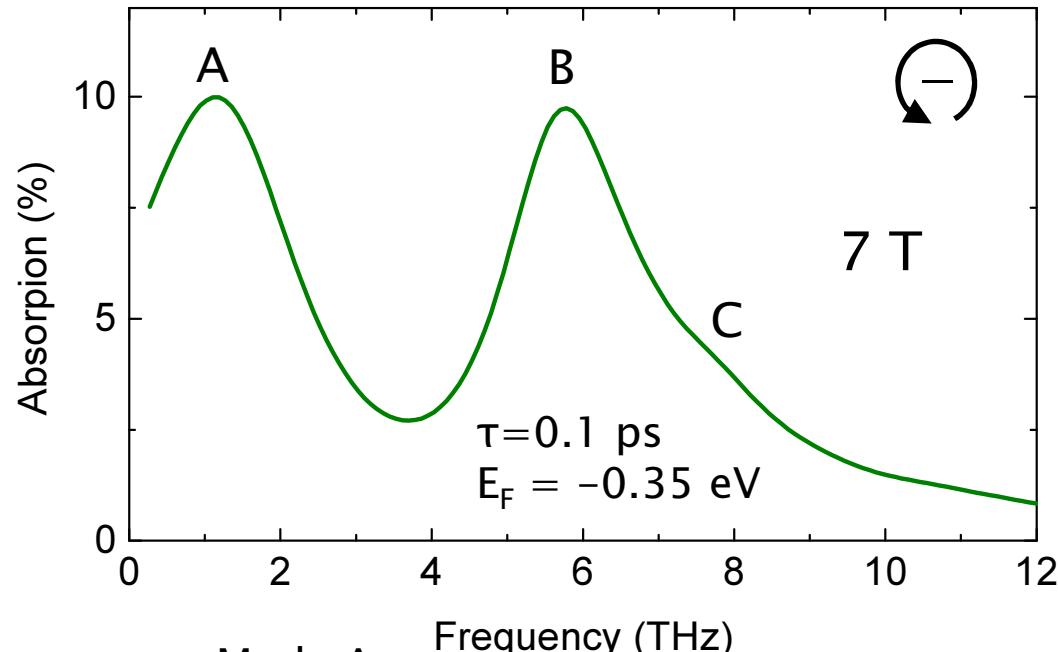


Solid symbols: experimental points
Solid lines: analytical theory *
Open circles: COMSOL simulation

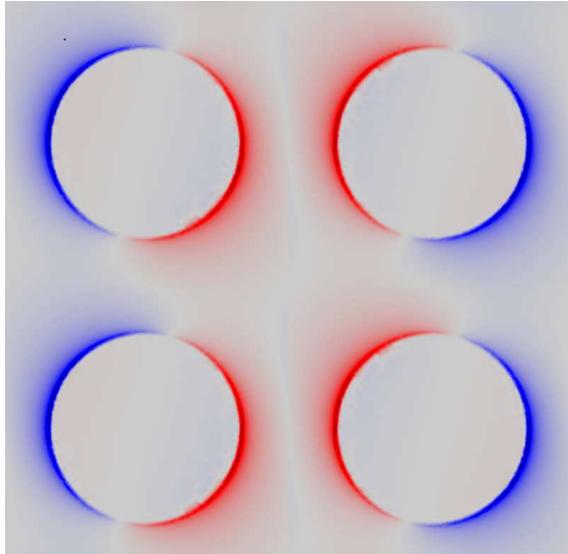


*S.A.Mikhailov and V.A. Volkov, Phys. Rev. B 52, 17260 (1995)
*S.A.Mikhailov, Phys. Rev. B 54, 14293 (1996)

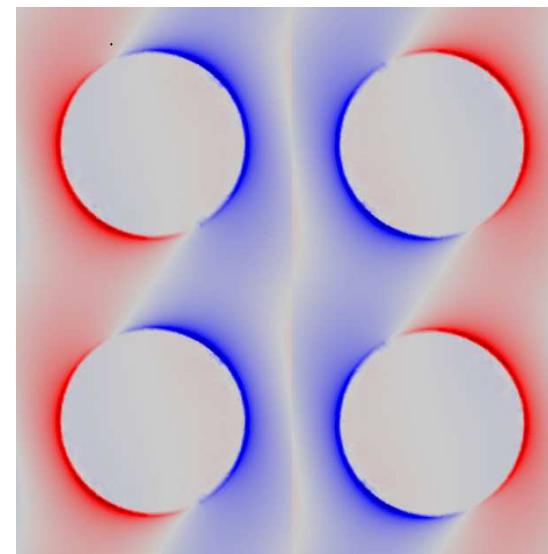
Simulated field profiles in graphene antidots



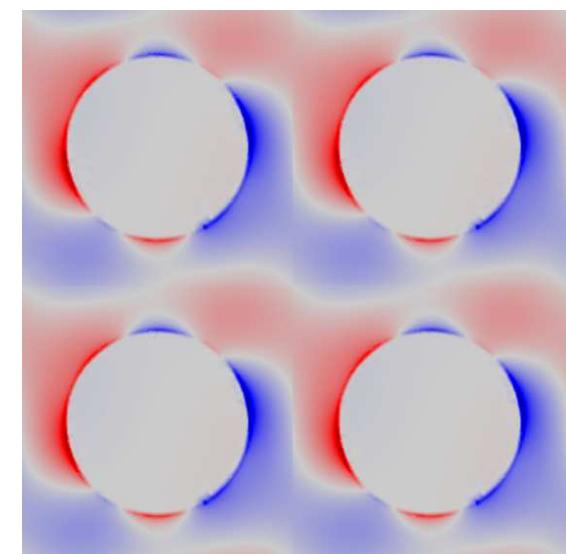
Mode A
(edge magneto-plasmon)



Mode B

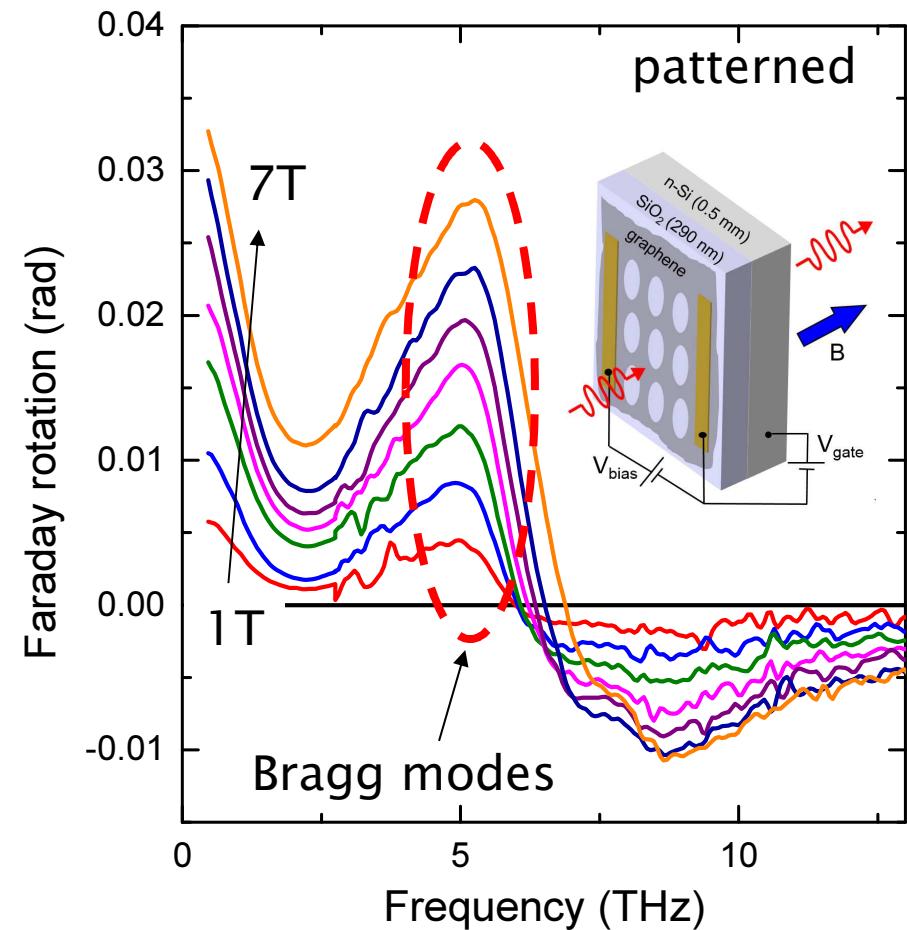
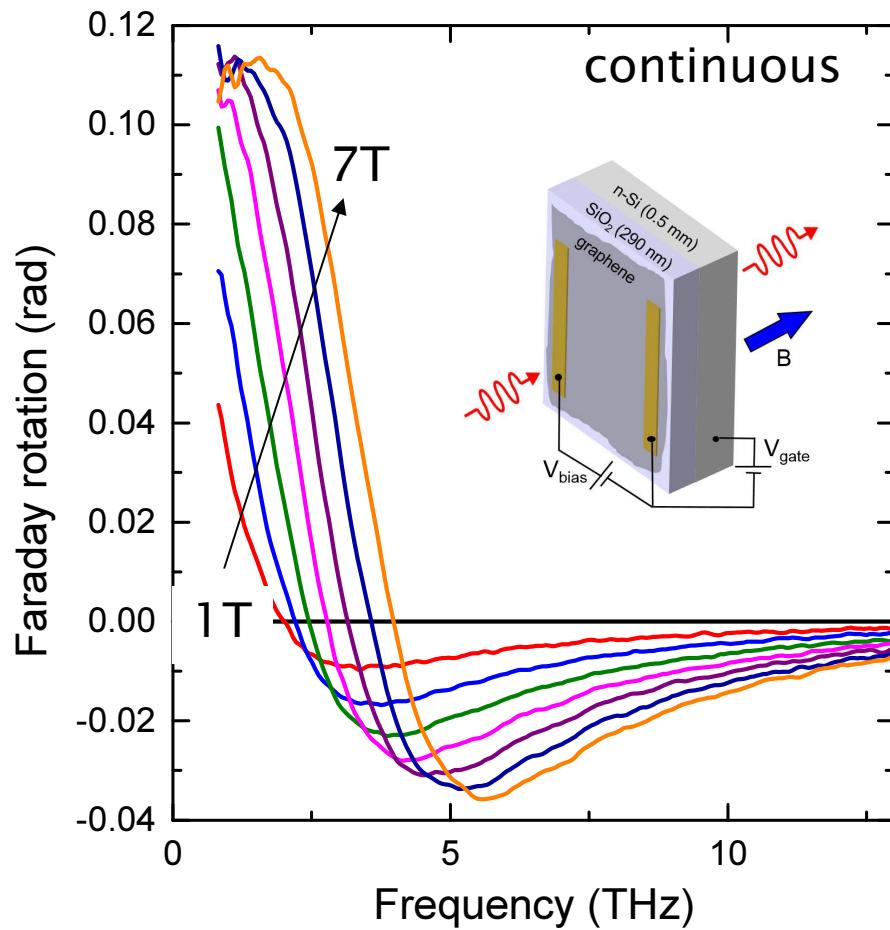


Mode C



Rich graphene
magneto-plasmon
physics !

Faraday rotation in continuous and patterned graphene



Patterning blue-shifts frequency of maximum Faraday rotation

Passive graphene-based THz elements

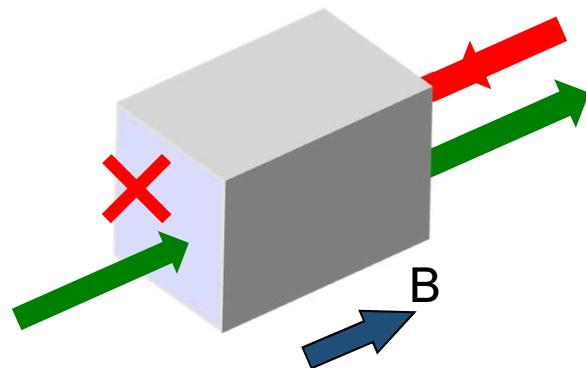
THz technology is lacking efficient passive devices:

- + Reciprocal: modulators, polarization converters etc.
- + Non-reciprocal: isolators, circulators etc.

Graphene:

- + Very efficient for manipulating THz waves
- + Ultrathin (magneto-THz effects occurs in an atomically thin layer)
- + Electrostatically switchable -> new functionalities

Optical isolator (diode, valve etc.)



- Critical element in many applications
(communications, lasers, optical computing etc.)
- Uses non-reciprocal magneto-optical effects
(Faraday rotation or magnetic circular dichroism)
- Often very bulk (a few cm thick)
- Difficult to invert

Microwave (< 150 GHz)
(based on ferrites)



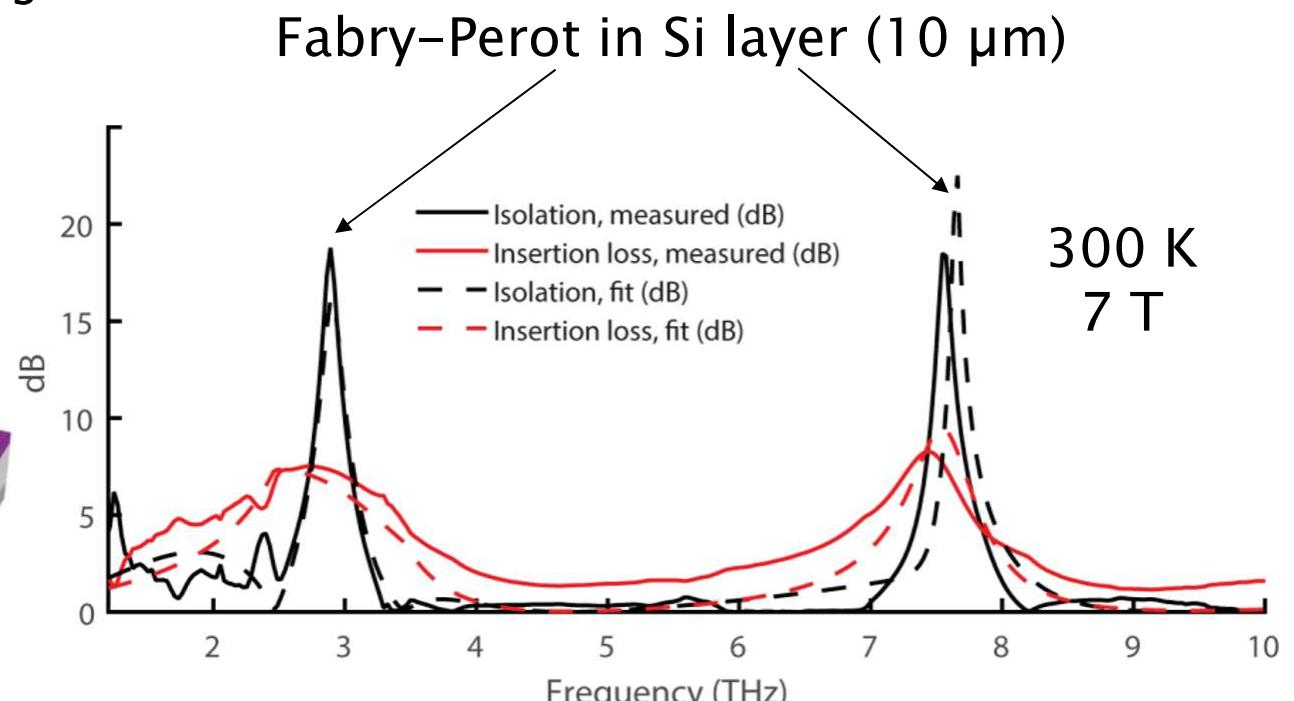
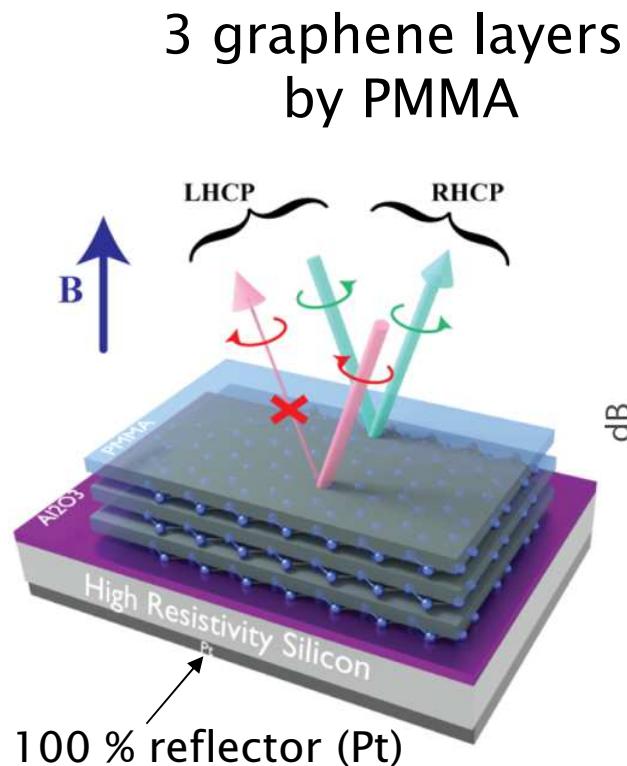
THz
(1-10 THz)

Nothing !!!

MIR-visible (> 15 THz)
(based on magnetic glasses)



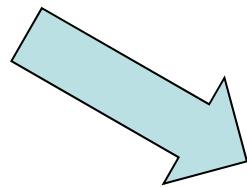
First prototype THz graphene-based isolator



- isolation > 18 dB
- insertion loss < 7 dB
- operates in reflection

Reducing the B-field is imperative for applications

7 T



<1.5 T



Summary

⊕ Handedness resolved magneto-infrared spectroscopy

J. Levallois et al., Rev. Sci. Instrum. 86, 033906 (2015)

⊕ Suppressed MCD and valley-polarized absorption in Bi

P.J. de Visser, J. Levallois et al. Phys. Rev. Lett. 117, 017402 (2016)

⊕ Electrically controlled terahertz MCD and FR in graphene

J.-M.Poumirol et al., Nature Communications, in press

⊕ Towards graphene-based magneto-optical THz devices

M. Tamagnone et al., Nature Commun. 7, 11216 (2016)

PhD and Postdoc positions available !!!



UNIVERSITÉ
DE GENÈVE

FNSNF
FONDS NATIONAL SUISSE
DE LA RECHERCHE SCIENTIFIQUE